



School on magnetism, Cluj, September 2007

# STM and spectroscopy of nanosized ferromagnetic structures

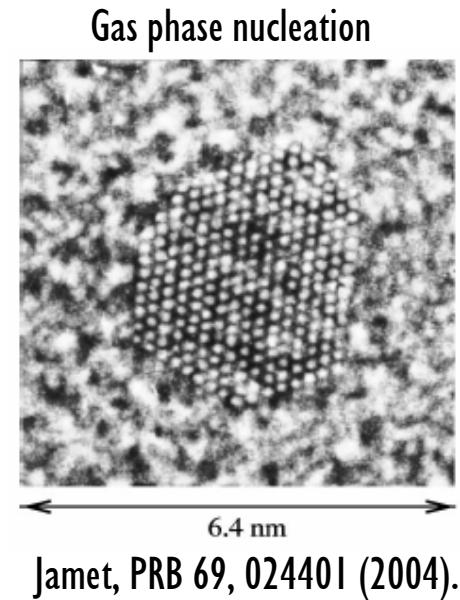
Guillemin Rodary

(Max Planck Institute, Halle, Germany)

# Ferromagnetic nanostructures

- $L_{sample} \approx L_{exch} \approx L_{domain\ wall}$   
⇒ monodomaine (Stoner-Wohlfarth switching ?)

Bonet, PRL 83, 4188 (1999)

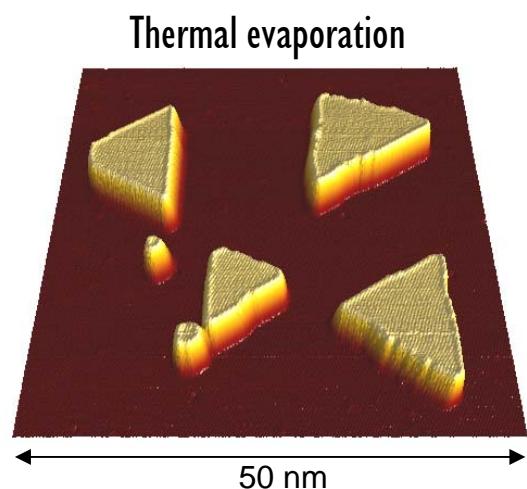


- Temperature could overcome anisotropy  $kT \approx KV$   
⇒ superparamagnetism

Bean, JAP 30, 120S (1959)  
Néel, Ann. Geophys. 5, 99 (1949)

- Atoms with low coordination  
⇒  $K_{surface}$  or  $M$  could be very high

Gambardella, Science 300, 1130 (2003)



- Quantum effects (discrete states, collective tunneling)

Bernard-Mantel, APL 89, 062502 (2006)  
Wernsdorfer, PRL 79, 4014 (1997)

# Probing nanomagnetism

## Imaging

See review Freeman, Science 294, 1484 (2001)

	Sensitive to	Typical resolution	Specificity
MOKE	M	500nm	Easy to use and cheap Argyle, JAP 87, 6487 (2000)
XMCD-PEEM	M	<10nm	Element specific, dynamic, synchrotron Vogel, PRB 72, 220402 (2005)
SEMPA	M	10nm	Vectorial M, surface Allenspach, JMMM 129, 160 (1994)
Lorentz	$\nabla B$	<10nm	Average over sample, no field Chapman, JMMM 200, 729 (1999)
MFM	$\nabla B$	50nm	Insulator OK, not quantitative Folks, APL 76, 909 (2000)
SP-STM	TMR	<1nm	No insulator, smooth surface, topography and spectro

## Magnetometry

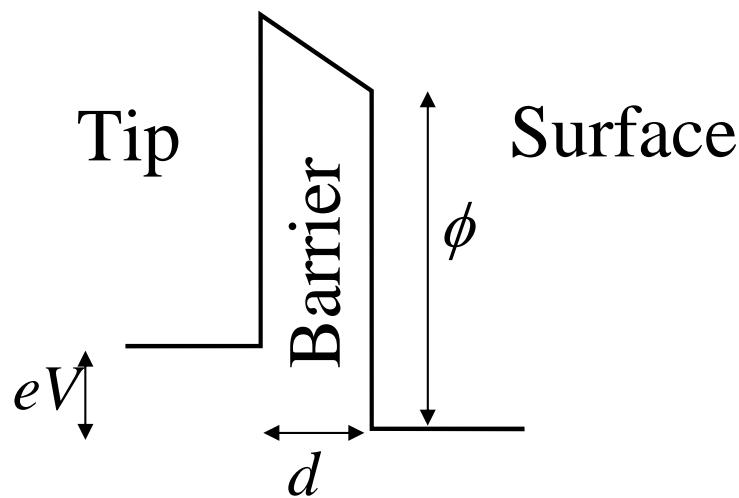
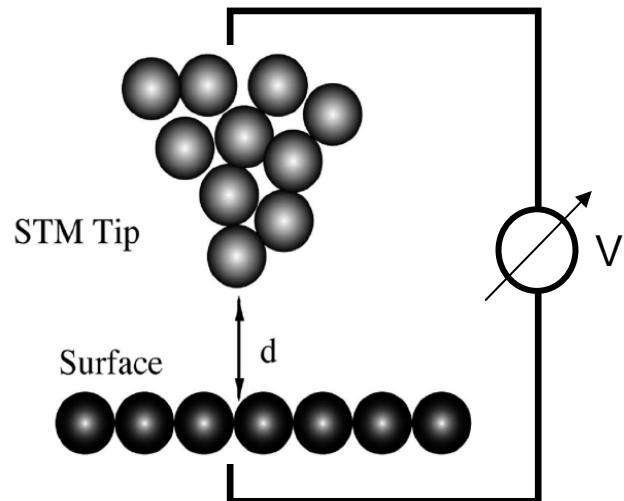
- SQUID, MOKE: thin films: OK  
nanoparticles : average over an assembly of identical objects Rohart, PRB 73, 165412 (2006)
- $\mu$ -SQUID: able to measure the switching field of a single nanostructure Jamet, PRB 69, 024401 (2004)

## Spin dependant transport

Lithography allows to take contact up to 10~100nm

Bernard-Mantel, APL 89, 062502 (2006)  
Ralph, PRL 74, 3241 (1995)

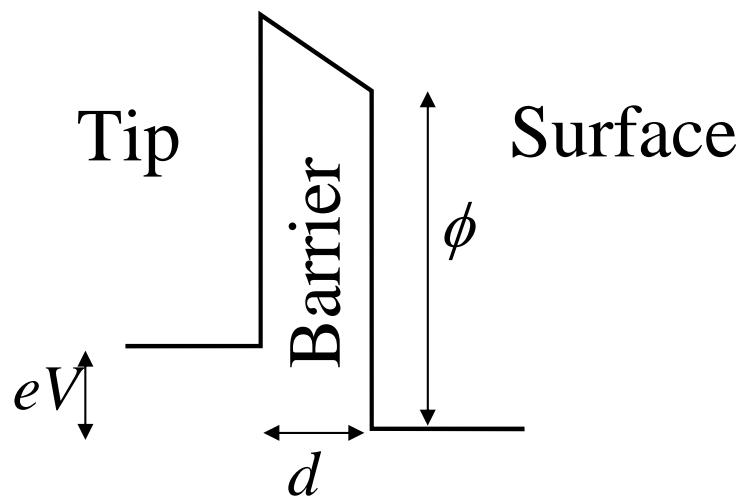
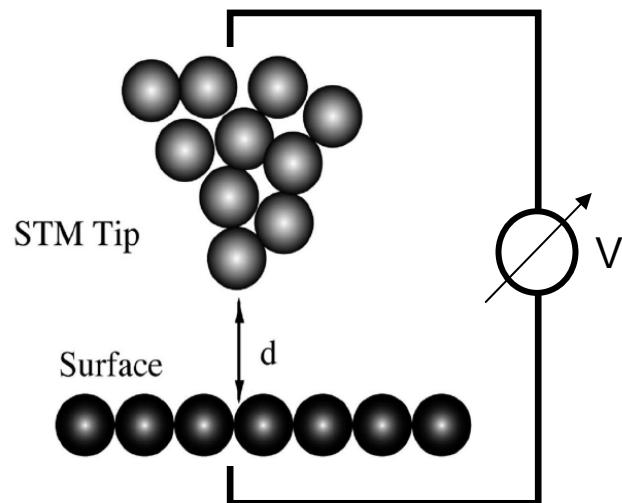
# Scanning tunneling microscopy



$$I_{tunnel} \propto e^{-d\sqrt{\phi-eV}}$$

Topography image a constant current

# Scanning tunneling microscopy

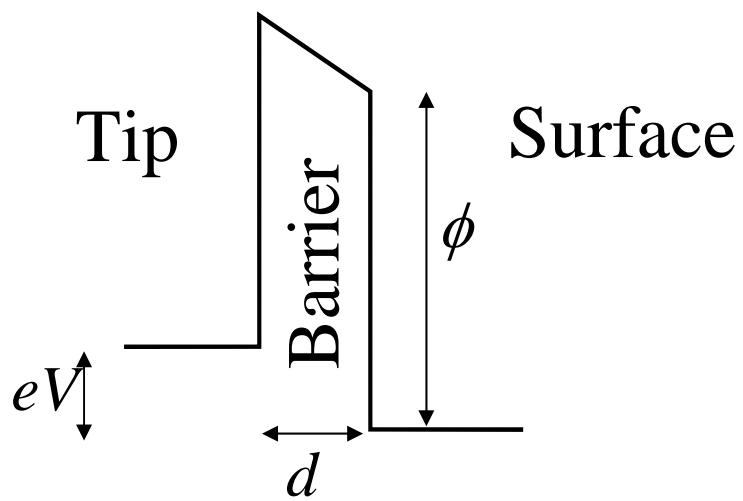
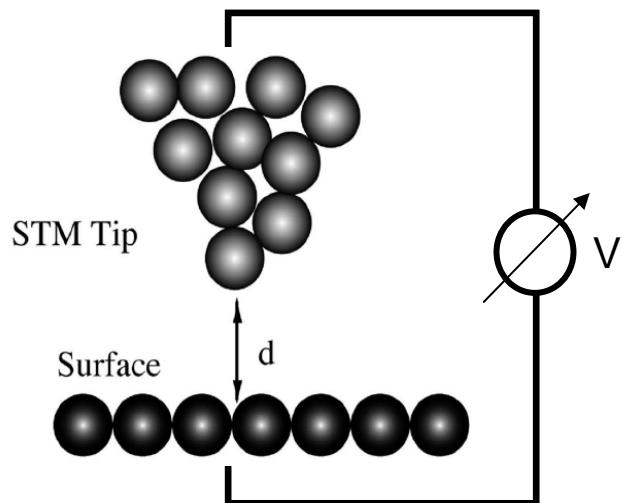


$$I_{tunnel} \propto e^{-d\sqrt{\phi-eV}}$$

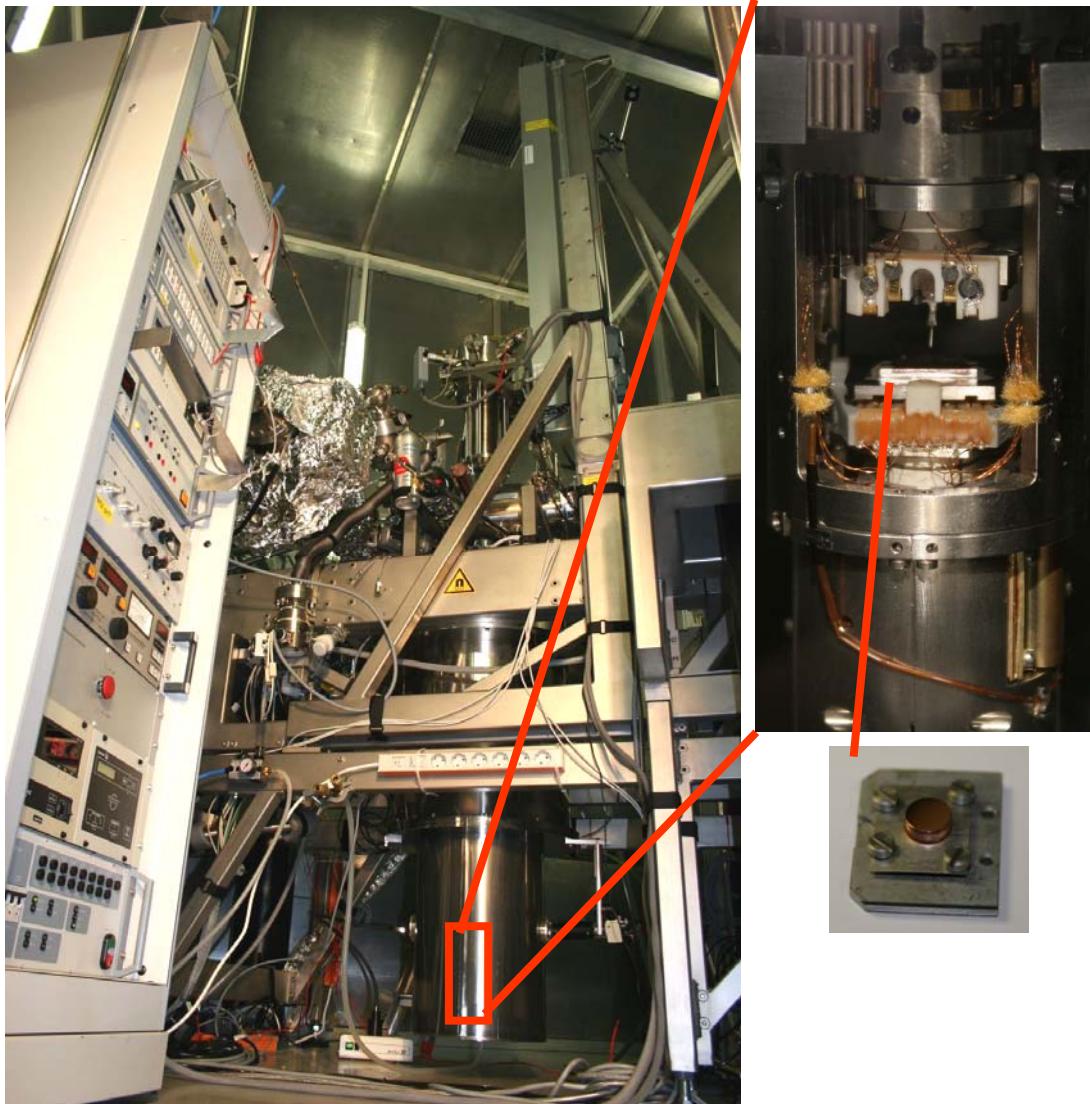


Topography image a constant current

# Scanning tunneling microscopy

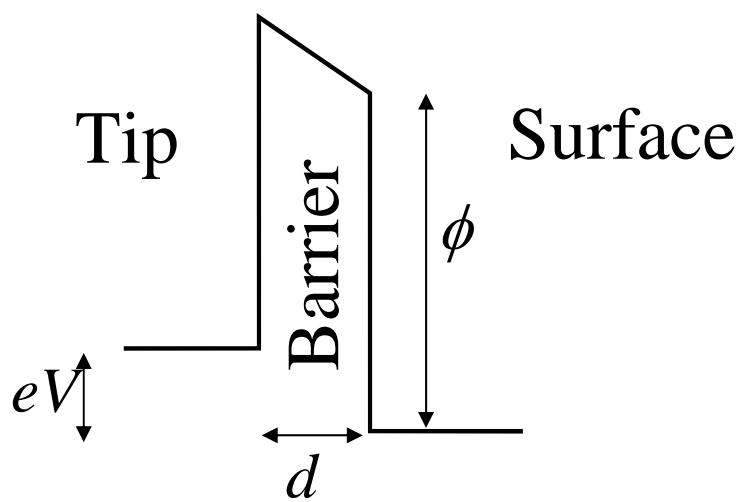
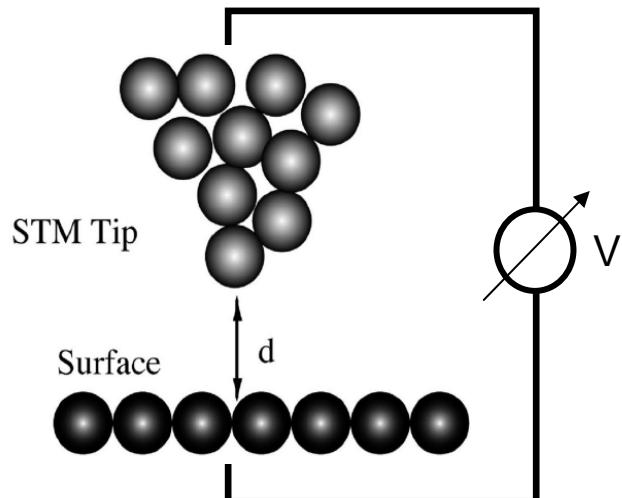


$$I_{tunnel} \propto e^{-d\sqrt{\phi-eV}}$$



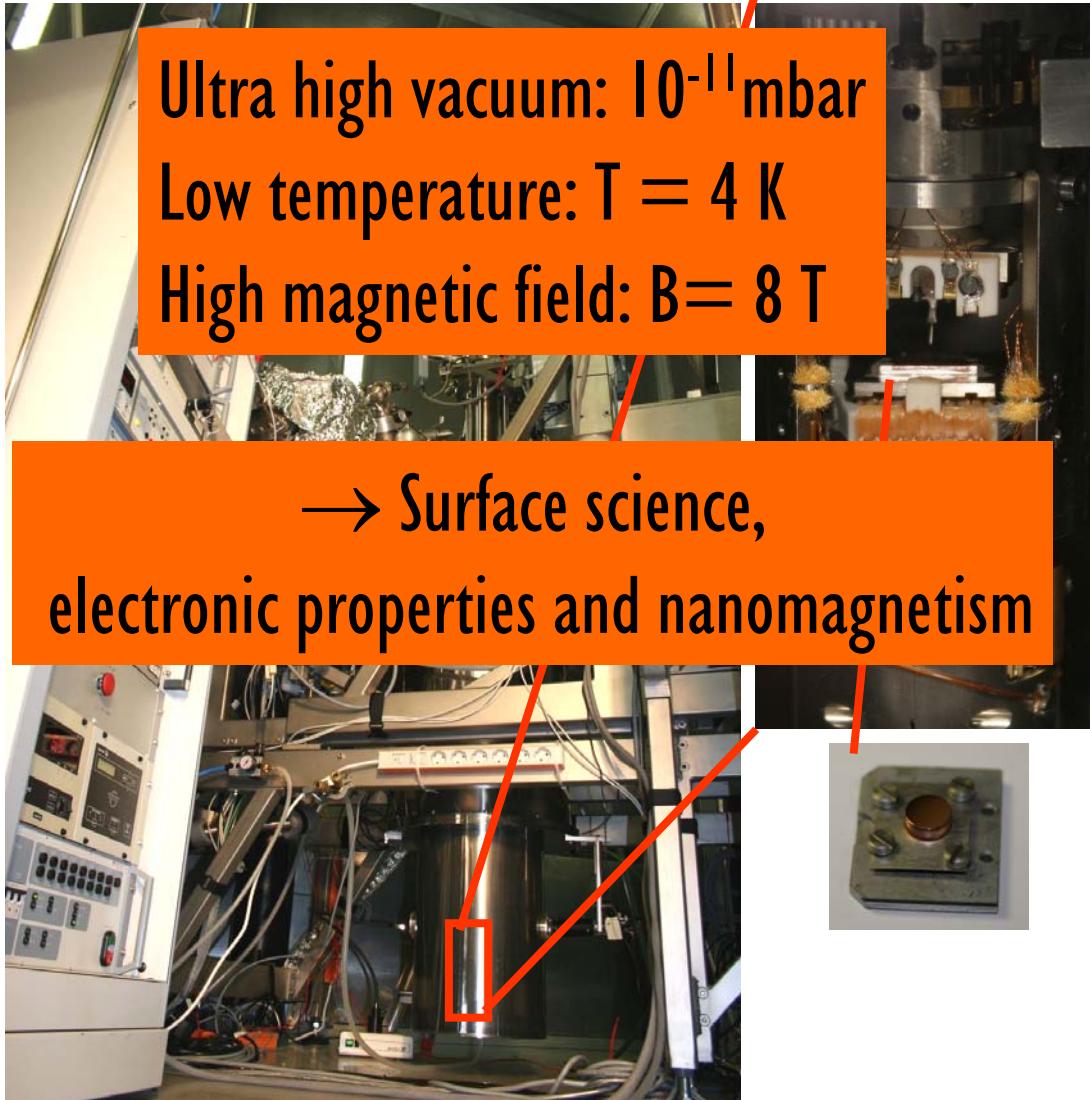
Topography image a constant current

# Scanning tunneling microscopy



$$I_{tunnel} \propto e^{-d\sqrt{\phi-eV}}$$

Topography image a constant current



# Growth of nanostructures studied by STM

## Nanodots

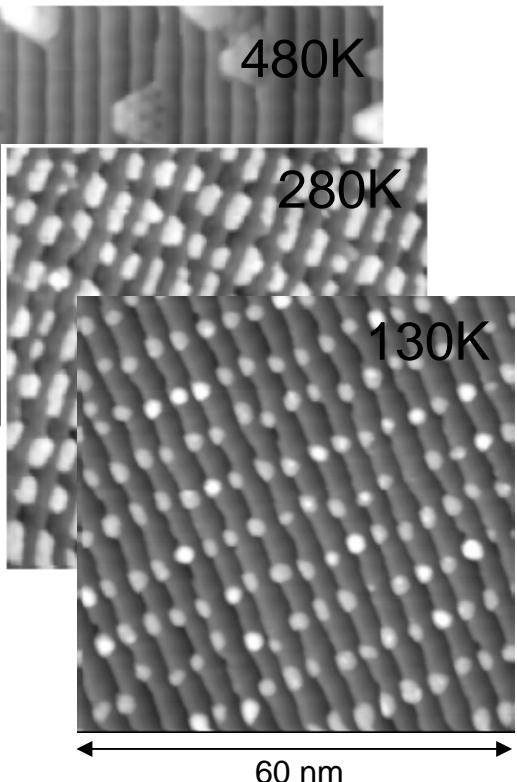
Co/Au(788)

Repinin, EPL 58, 730 (2002)

480K

280K

130K

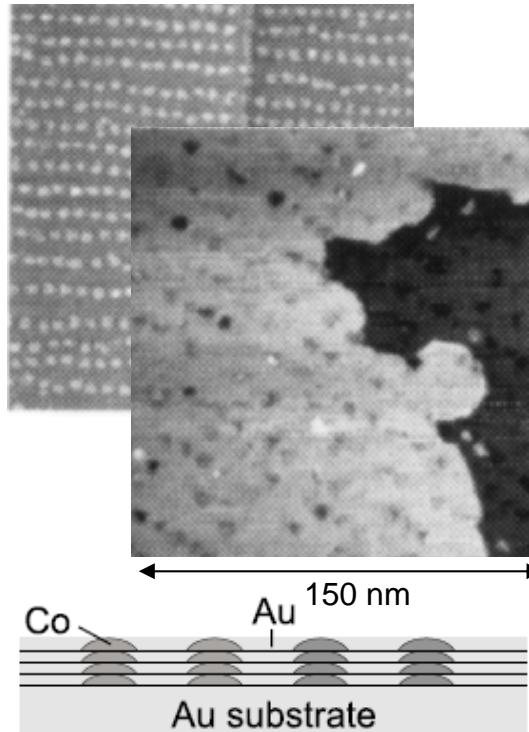


- Temperature growth  $\Rightarrow$  Diffusion coefficient + trap energy
- Periodical array of similar dots  $\Rightarrow$  Array =  $N \times$  single dot

## Nanopillars

Co/Au(111)

Fruchart, PRL 83, 2769 (1999)

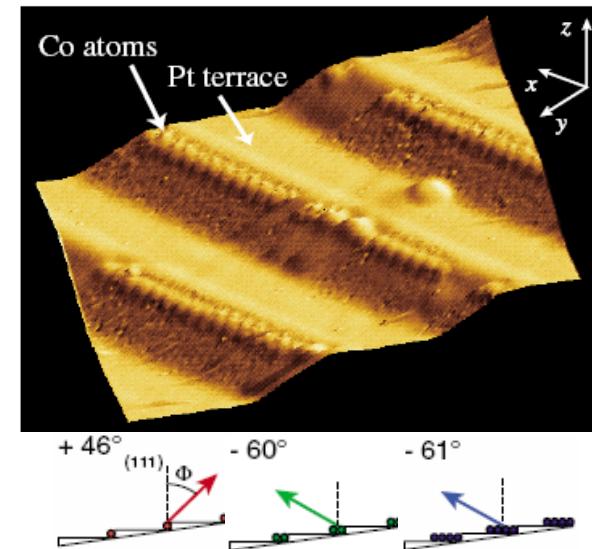


- 3D structures
- Aspect ratio 2:1
- Blocking temperature: from 20 K to 300K

## 1D chains

Co/Pt(997)

Gambardella, JPhysCondMat 15, 2533 (2003)



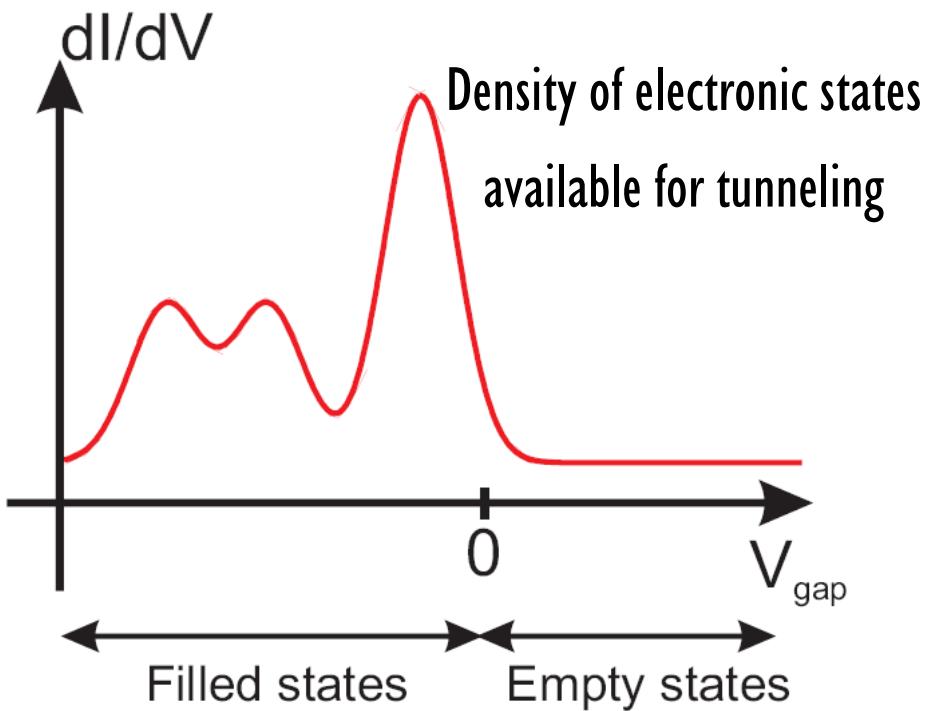
- Chains width of 1, 2 or 3 atoms
- Ferromagnetic behavior with very high magnetic moment
- Reduce dimensionality  $\Rightarrow$  strong magnetic anisotropy

# Scanning tunneling spectroscopy

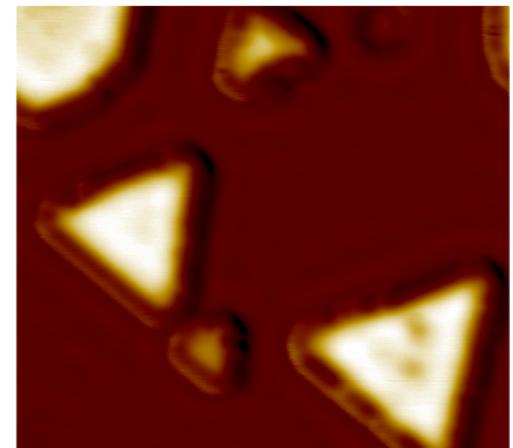
$$I(\mathbf{r})_{\text{tunnel}} \propto \int_0^{eV} \text{LDOS}(\mathbf{r}, E) dE$$

$$\text{LDOS}(\mathbf{r}, E) = \sum_v |\psi_v(\mathbf{r})|^2 \delta(E - E_v)$$

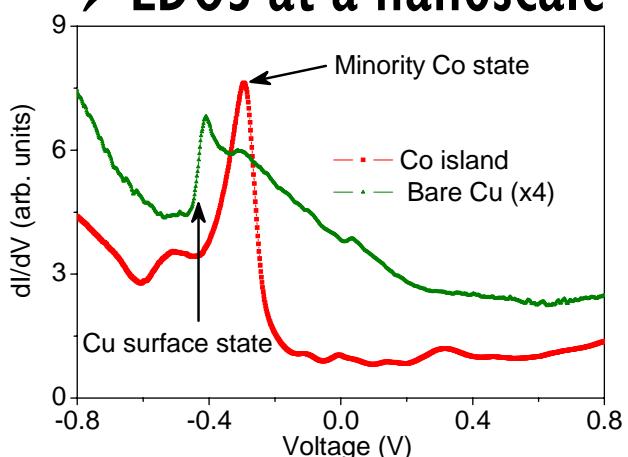
$$\frac{dI}{dV}(\mathbf{r}, E) \propto \text{LDOS}(\mathbf{r}, E)$$



LDOS map  
→ Electronic structures

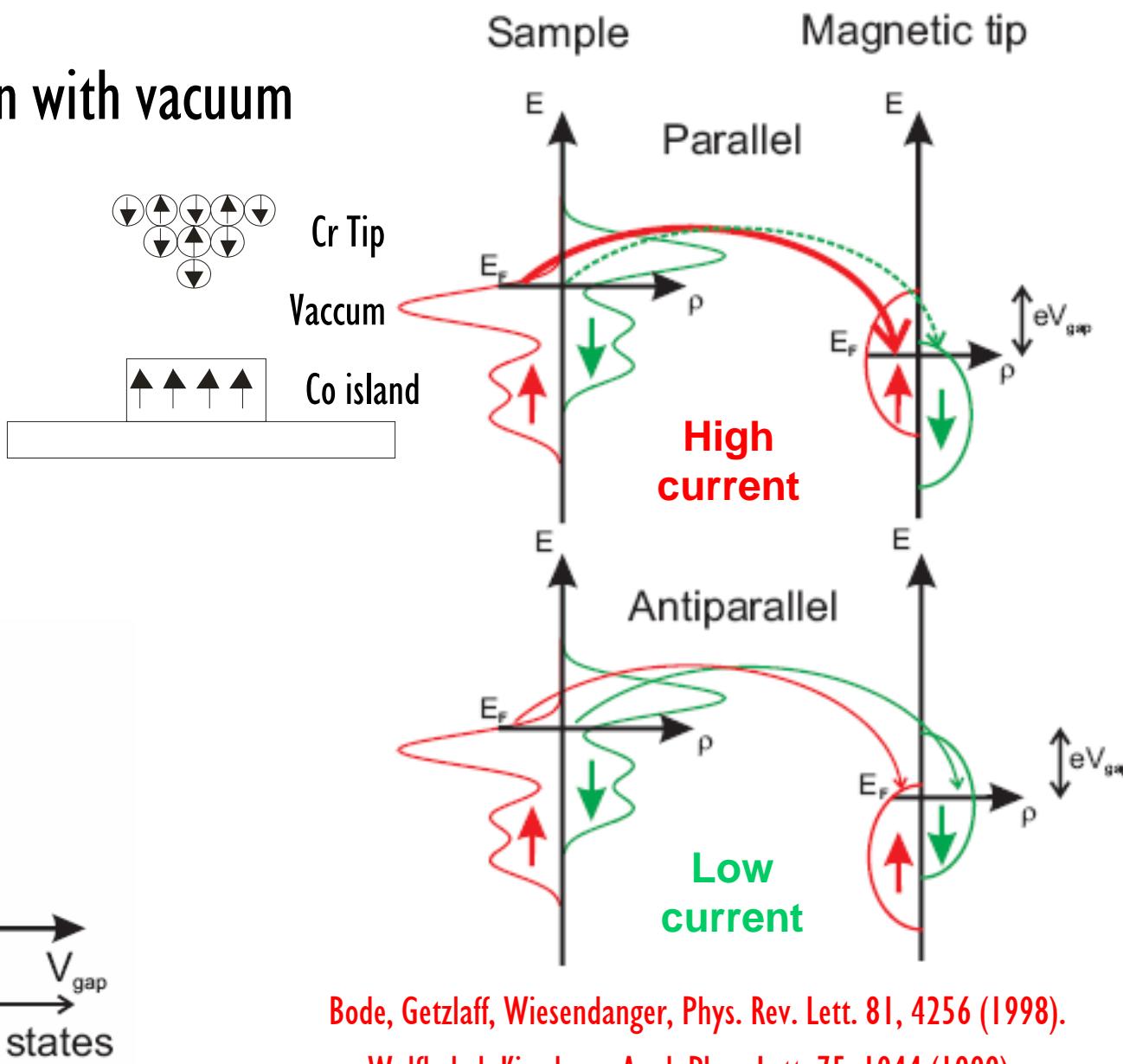
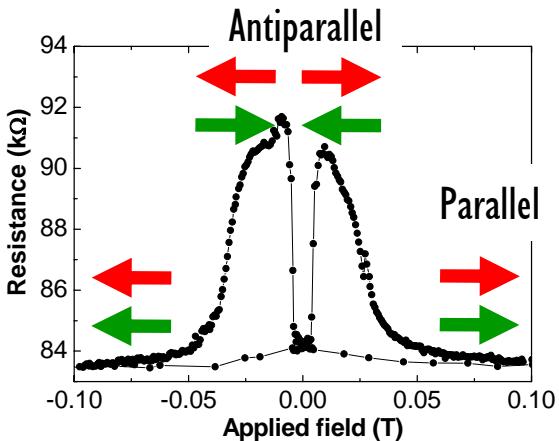


Point spectroscopy  
→ LDOS at a nanoscale



# Principle of Spin-Polarized STM

## Magnetic tunnel junction with vacuum

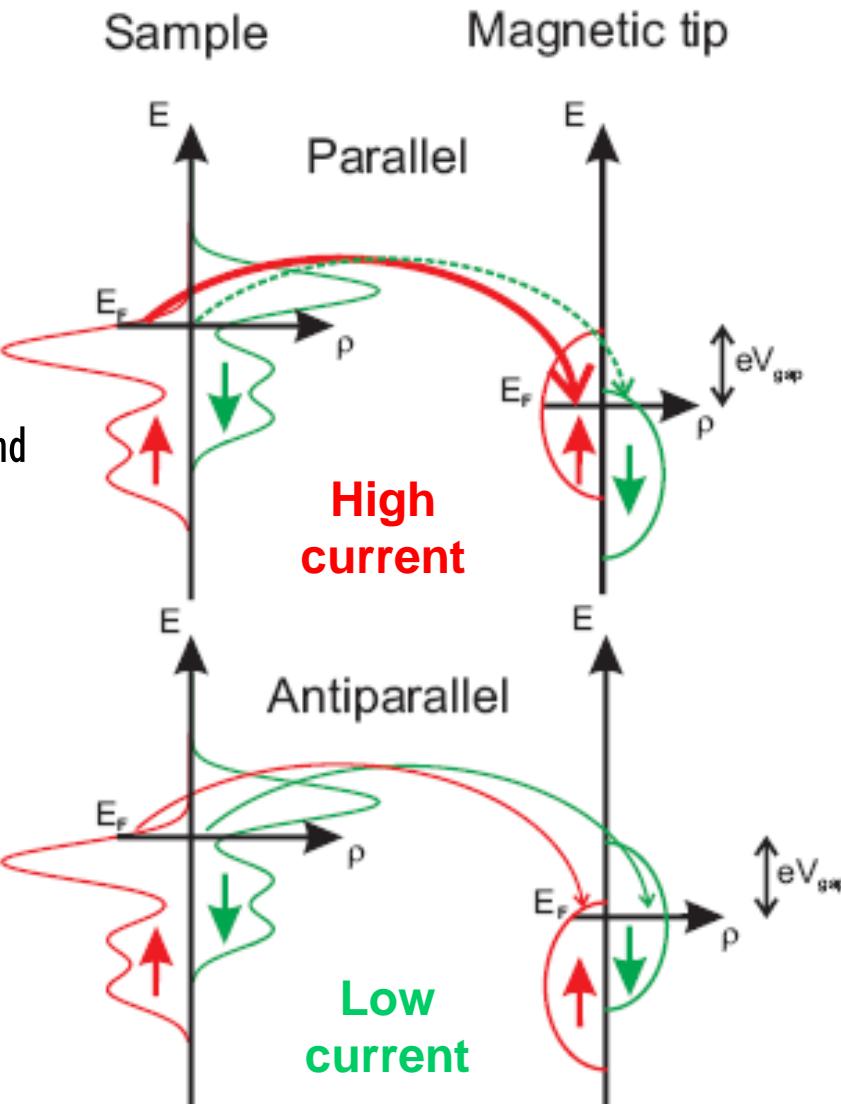
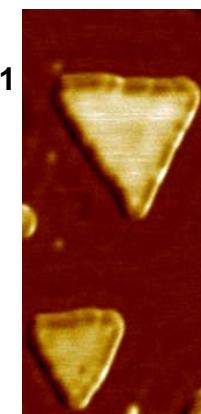
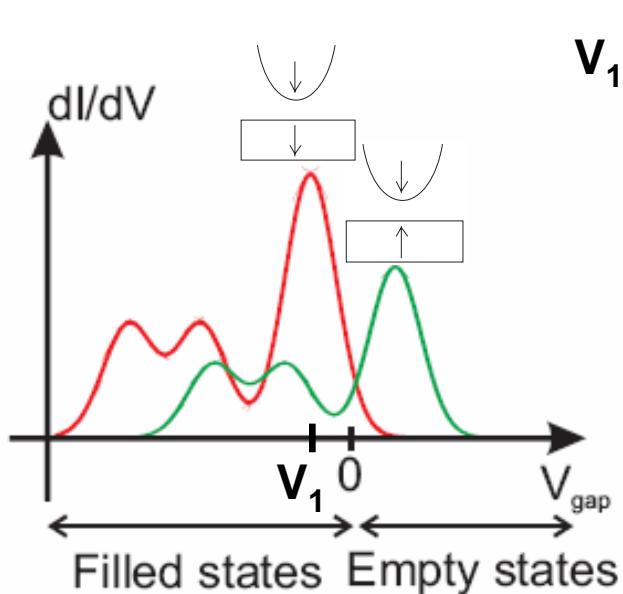
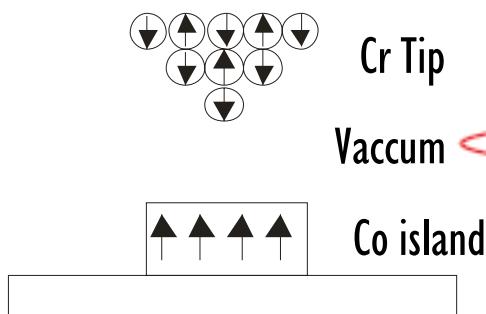
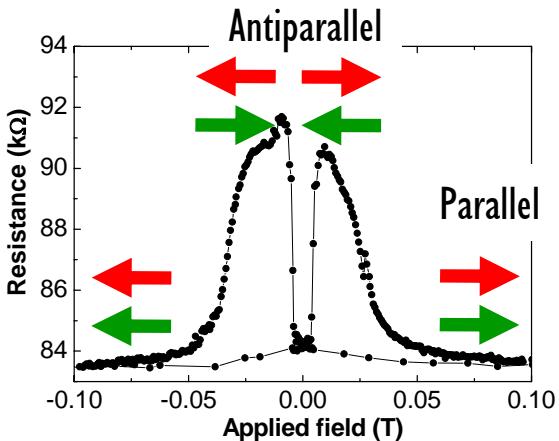


Bode, Getzlaff, Wiesendanger, Phys. Rev. Lett. 81, 4256 (1998).

Wulfhekel, Kirschner, Appl. Phys. Lett. 75, 1944 (1999)

# Principle of Spin-Polarized STM

## Magnetic tunnel junction with vacuum

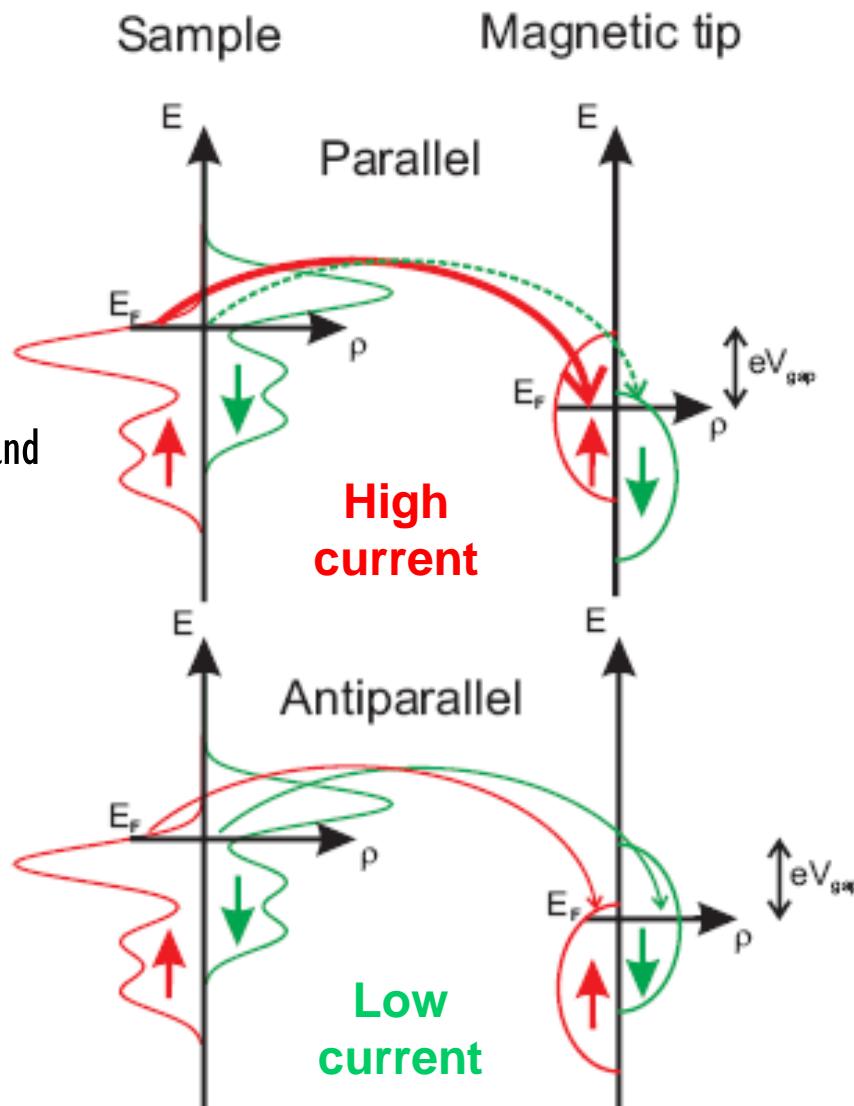
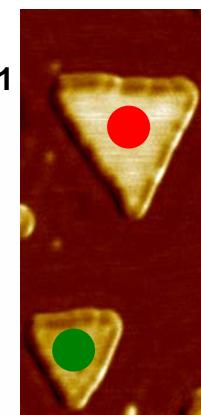
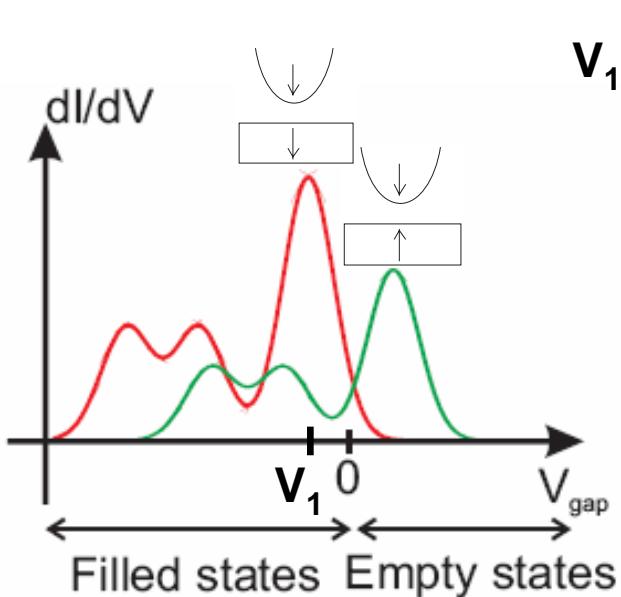
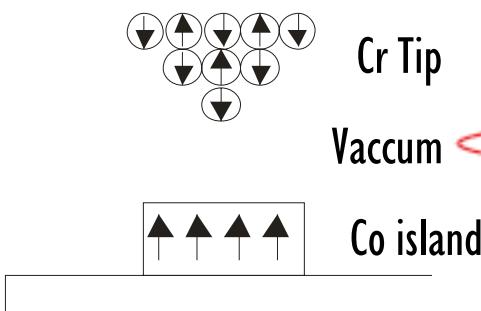
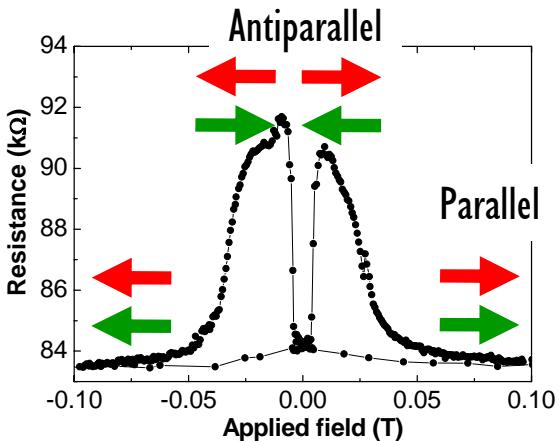


Bode, Getzlaff, Wiesendanger, Phys. Rev. Lett. 81, 4256 (1998).

Wulfhekel, Kirschner, Appl. Phys. Lett. 75, 1944 (1999)

# Principle of Spin-Polarized STM

## Magnetic tunnel junction with vacuum



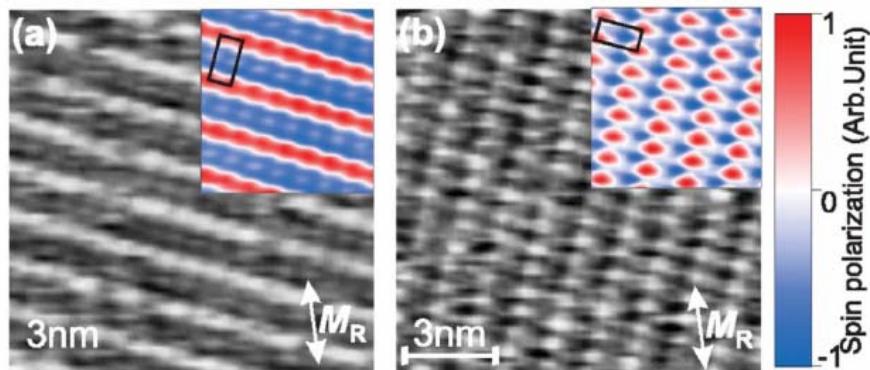
Bode, Getzlaff, Wiesendanger, Phys. Rev. Lett. 81, 4256 (1998).

Wulfhekel, Kirschner, Appl. Phys. Lett. 75, 1944 (1999)

# Nanomagnetism: imaging of spin structure

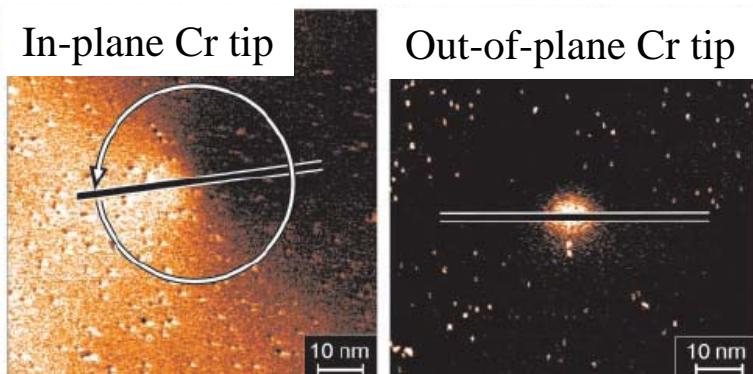
## Magnetic surface reconstruction

- “Spin maps” made at constant current and at fixed voltage
- Spin sensitivity of the tip in or out of plane



IML of Mn on Fe(001)  
Gao, PRL 98, 107203 (2007))

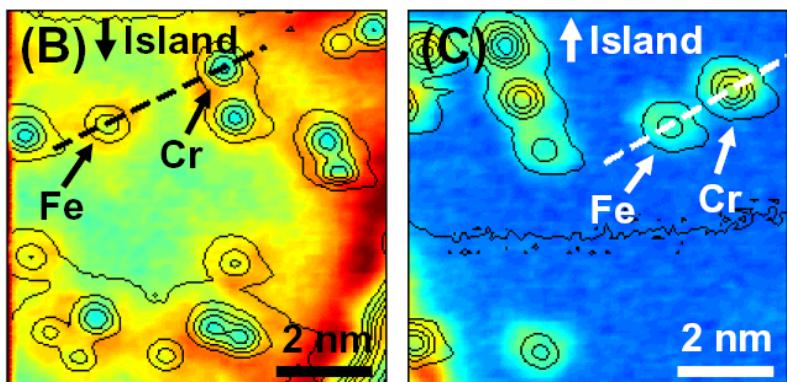
## Magnetic nanostructures



Vortex in Fe island on W(110),

Wachowiak, Science 298, 577 (2002)

## Single magnetic atoms

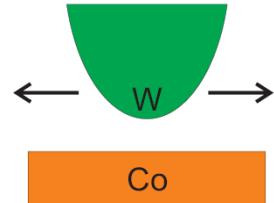


Atoms on Co islands

Yayon, PRL 99, 067202 (2007)

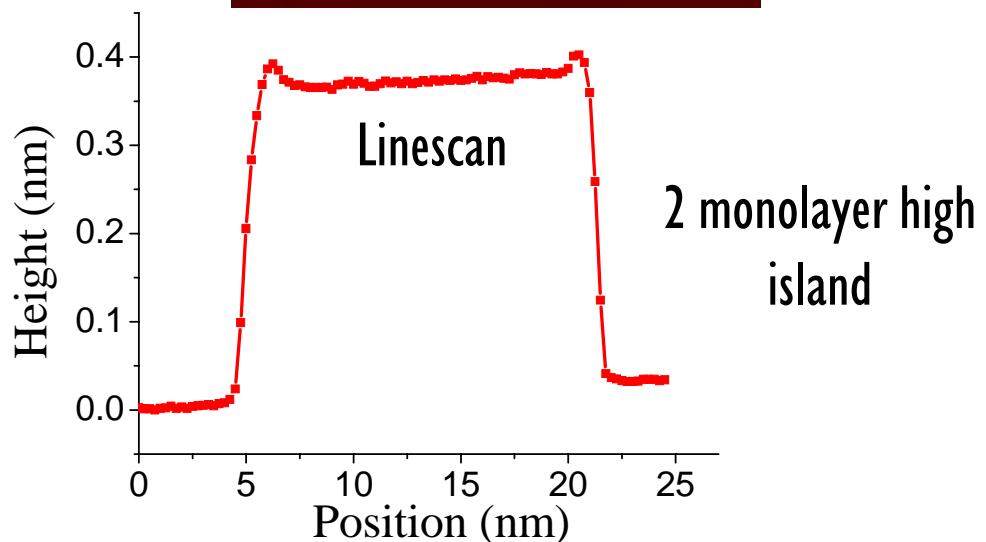
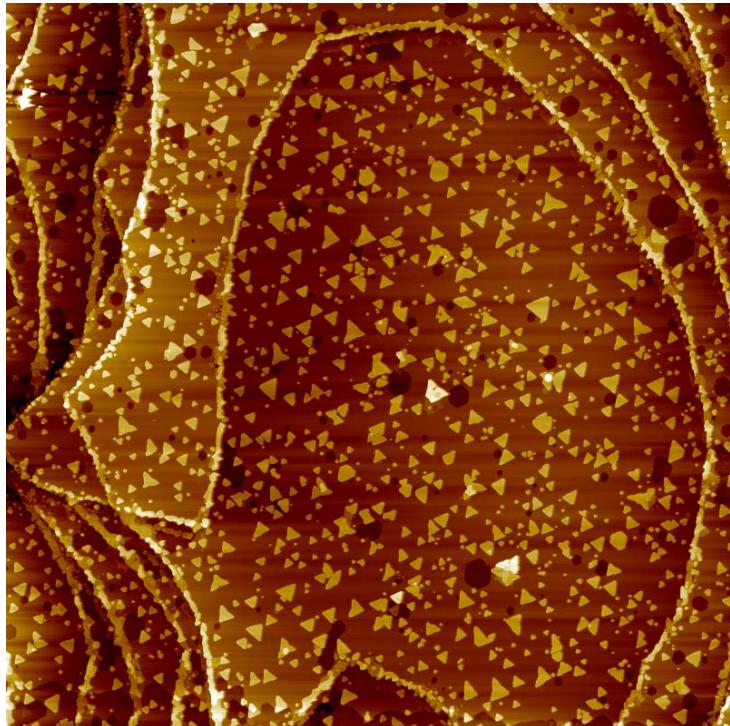
# Co island on Cu(111)

Co deposition at 300K on Cu(111)



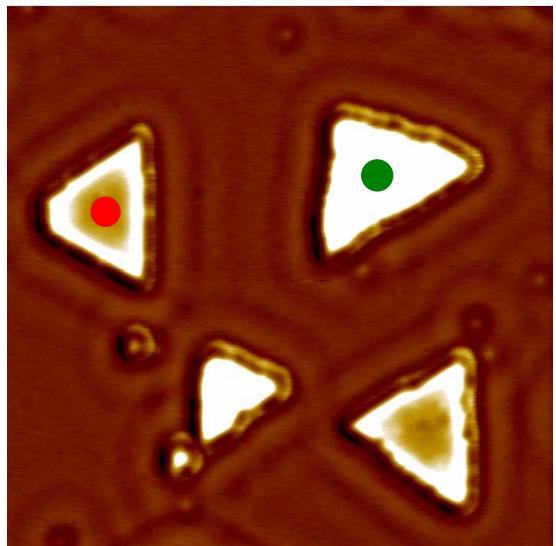
⇒ Triangular Co islands

⇒ Step edge decoration

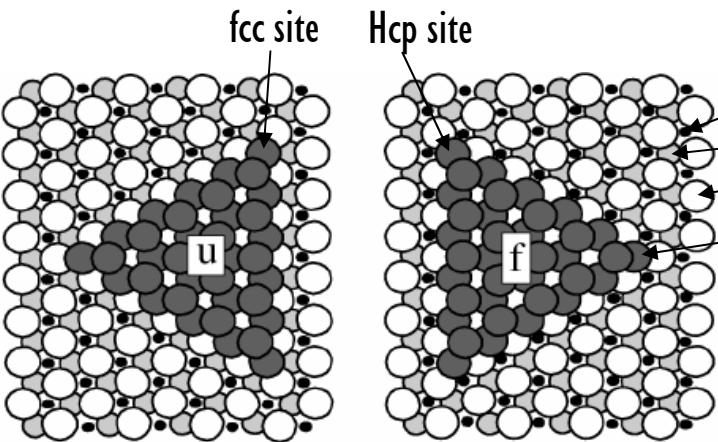


# Spectroscopy on a single island

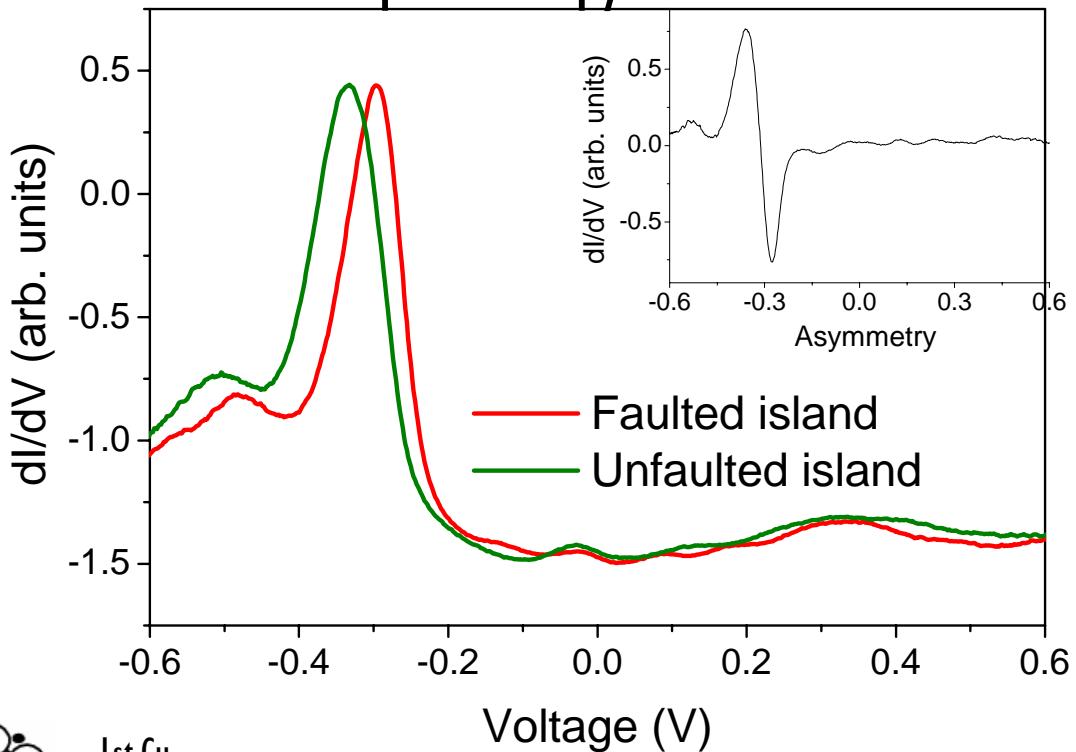
dI/dV image



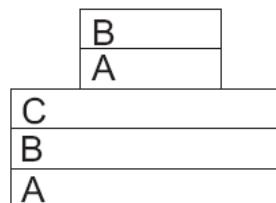
50 x 50 nm<sup>2</sup>, -0.36 V, 1 nA



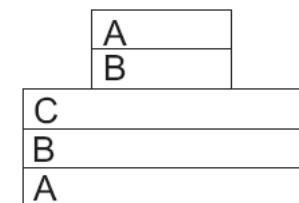
Point spectroscopy on the island



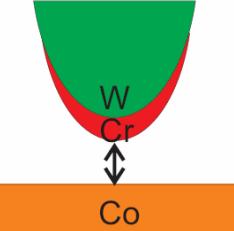
Unfaulted



Faulted

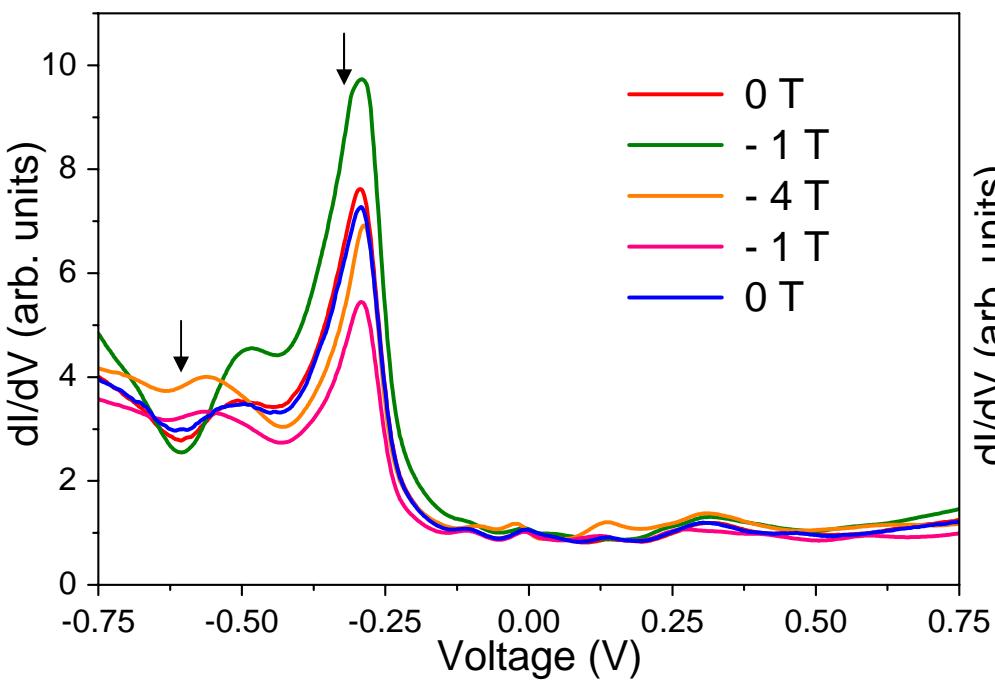


# Spectroscopy on a single island

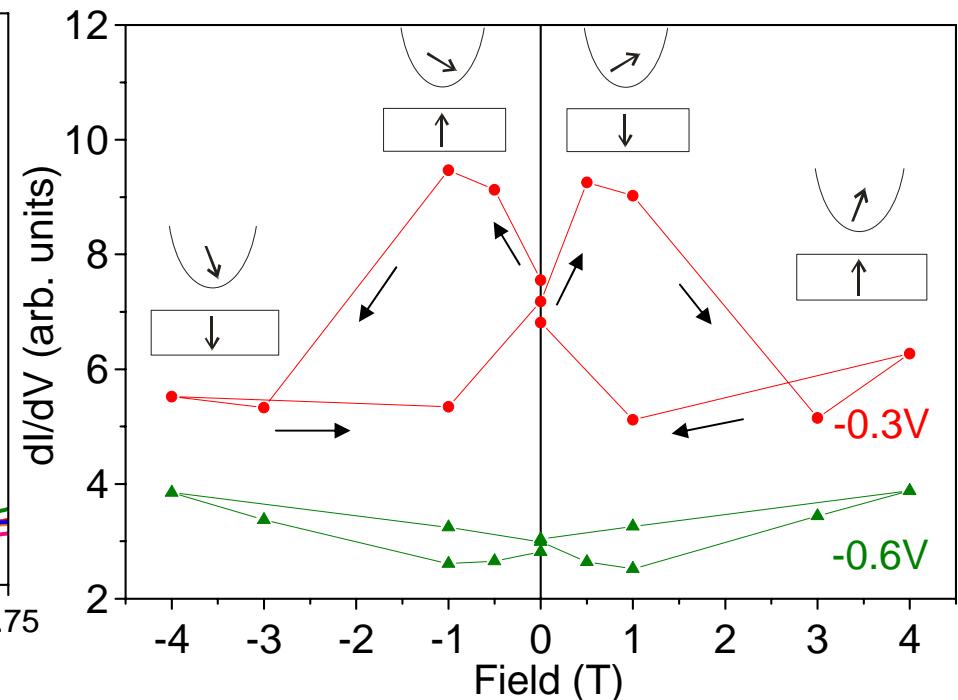


$I(V)$  and  $dI/dV(V)$  curves measured at island center

In field spectroscopy

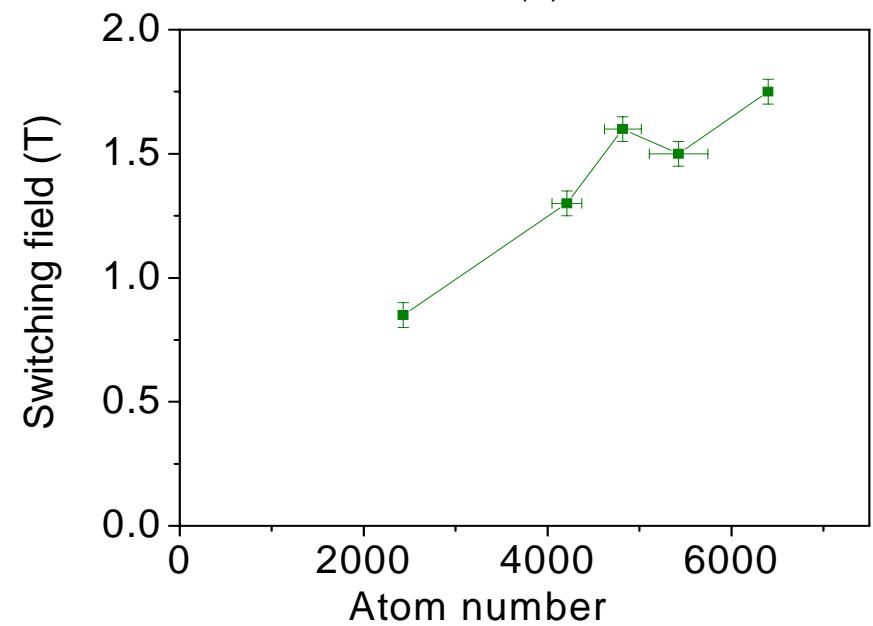
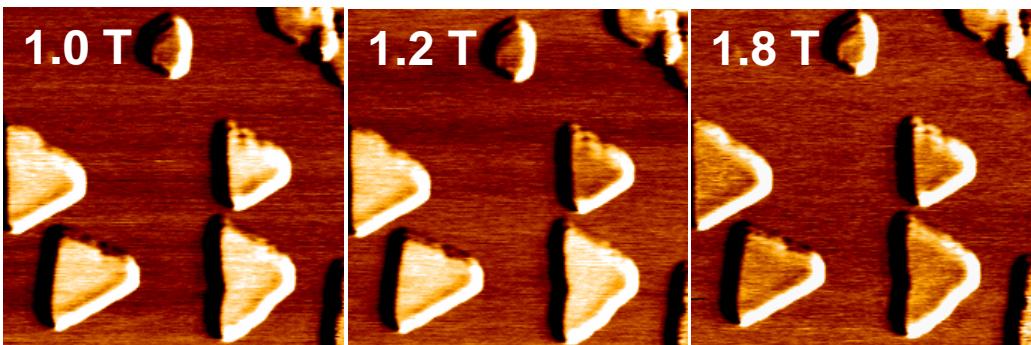
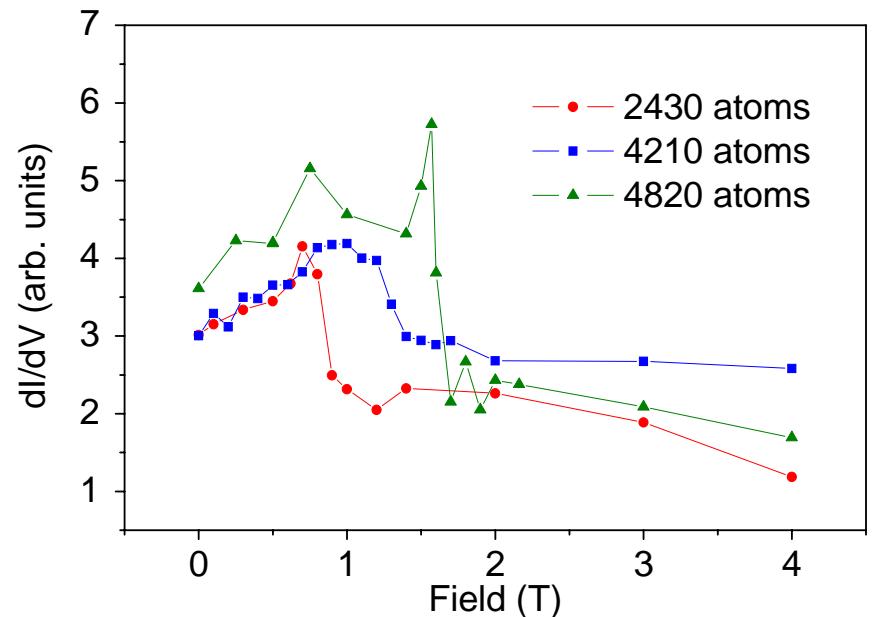


Extraction of the hysteresis cycle  
at different voltages

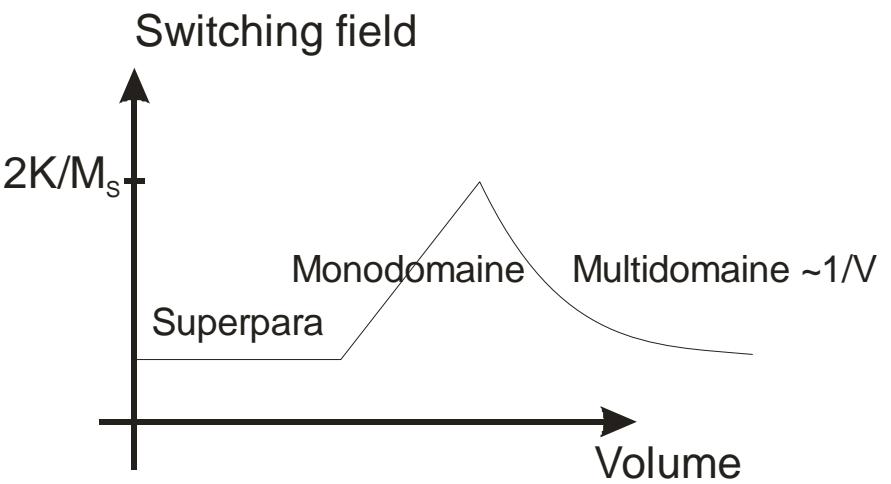


- TMR hysteresis loop of a single nanostructure
- Understanding the relative magnetic orientation of tip and sample
- Measure the TMR at a nanoscale

# Size dependence of the switching field

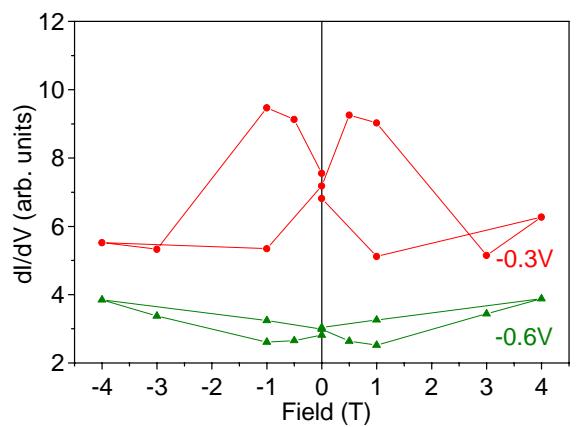
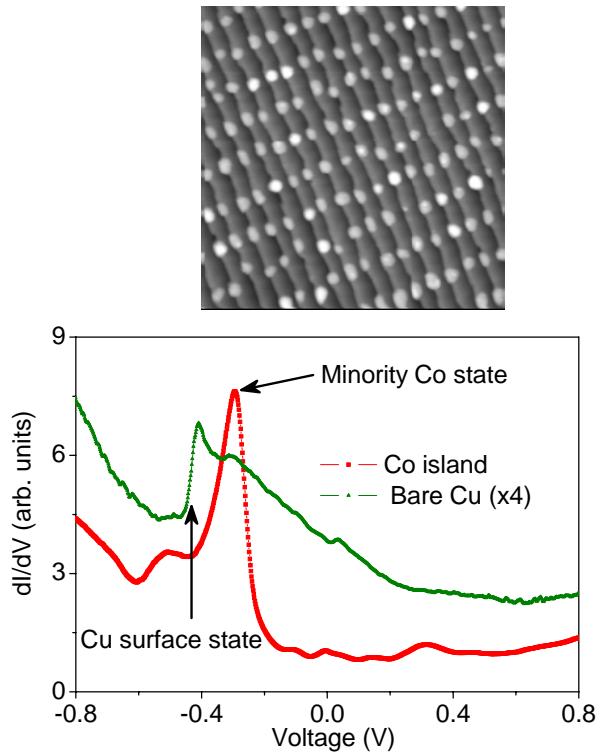
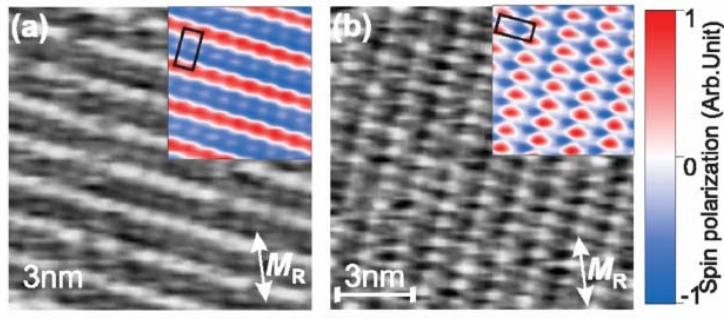


Regime between superparamagnetism  
and multi-domain island

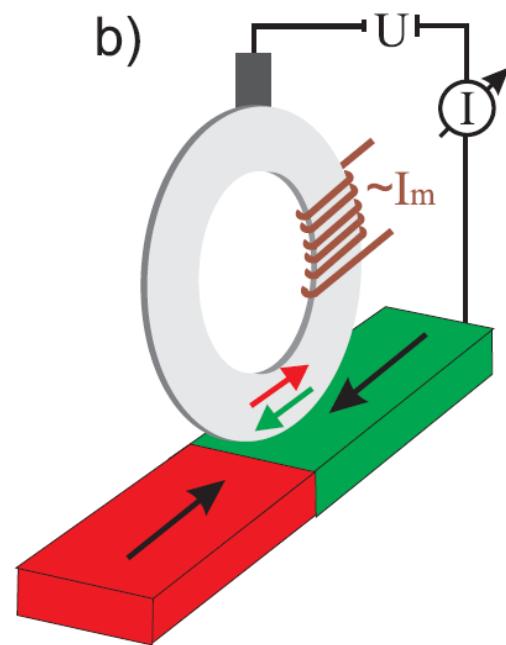
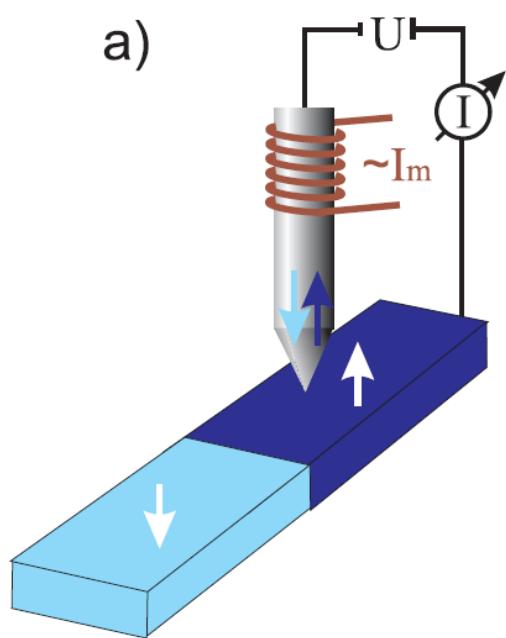


# Conclusion

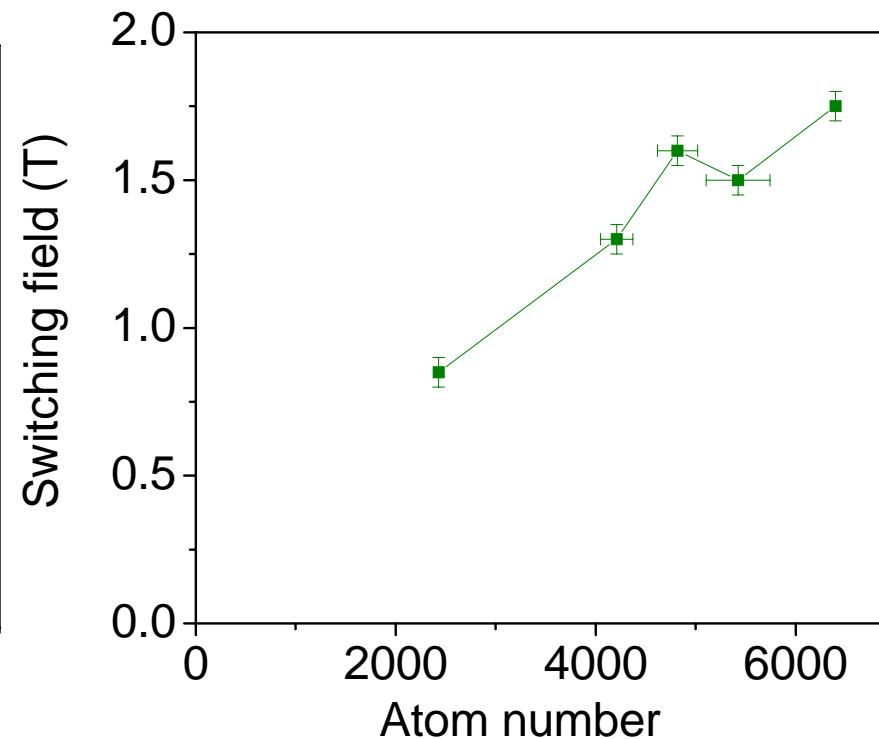
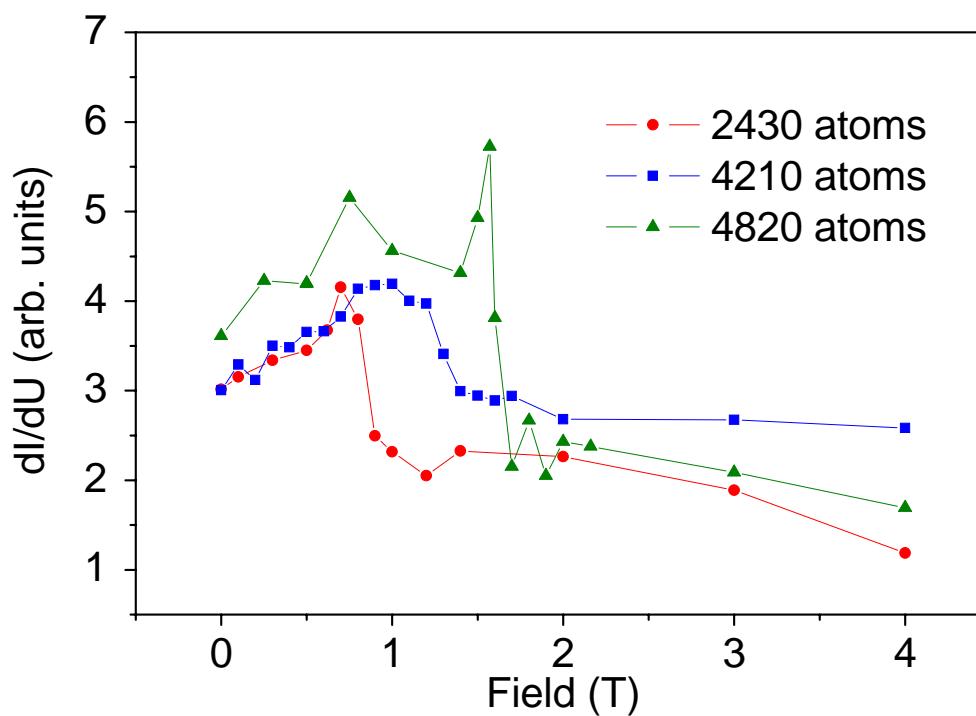
- STM: study of growth, structure and organization of ferromagnetic nanostructures (films, dots, pillars, chains...)
- STS: - mapping of the electronic structure (standing waves)
  - locales density of states on nanostructures
  - structure characterisation
- SP-STM: - spin map in and out of plane with atomic resolution
  - spin dependant transport (TMR) at a nanoscale
  - study of switching of a single nanoobject





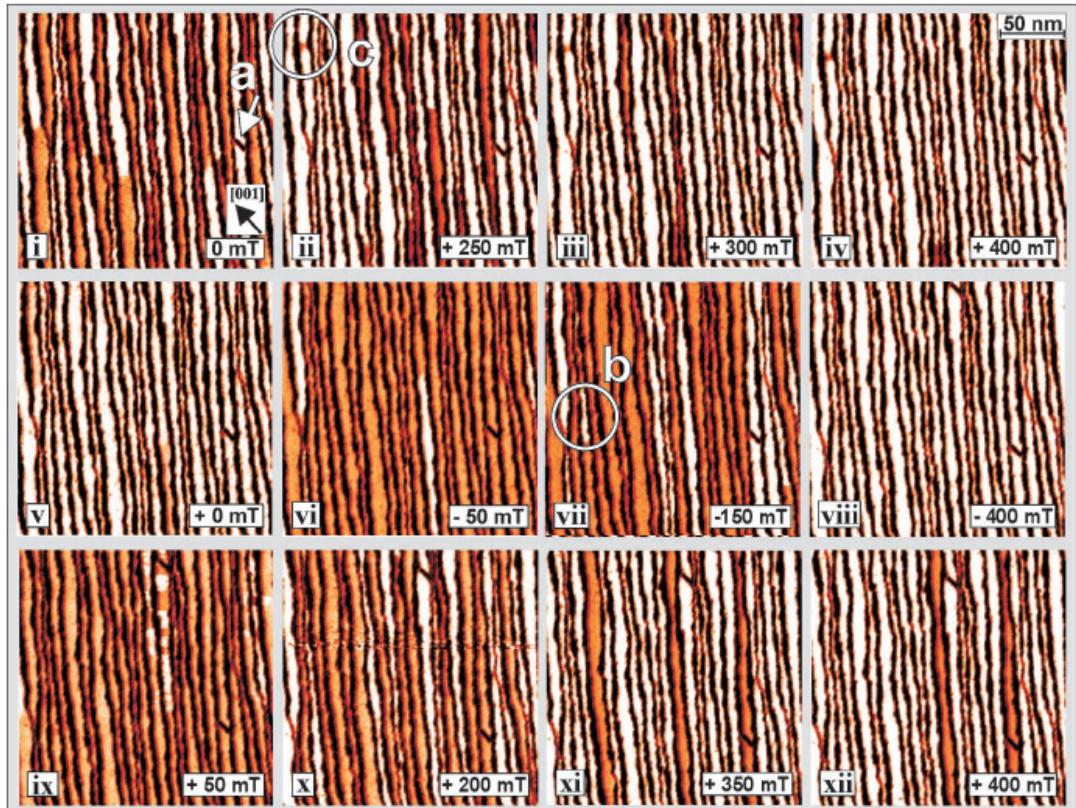


# Size dependence of the island switching field

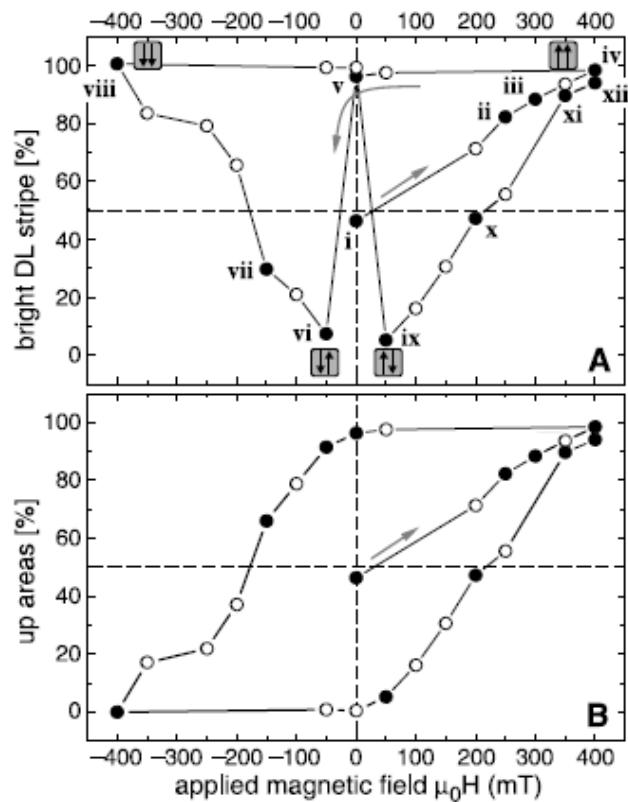


# Observation of Magnetic Hysteresis at the Nanometer Scale by Spin-polarized Scanning Tunneling Spectroscopy

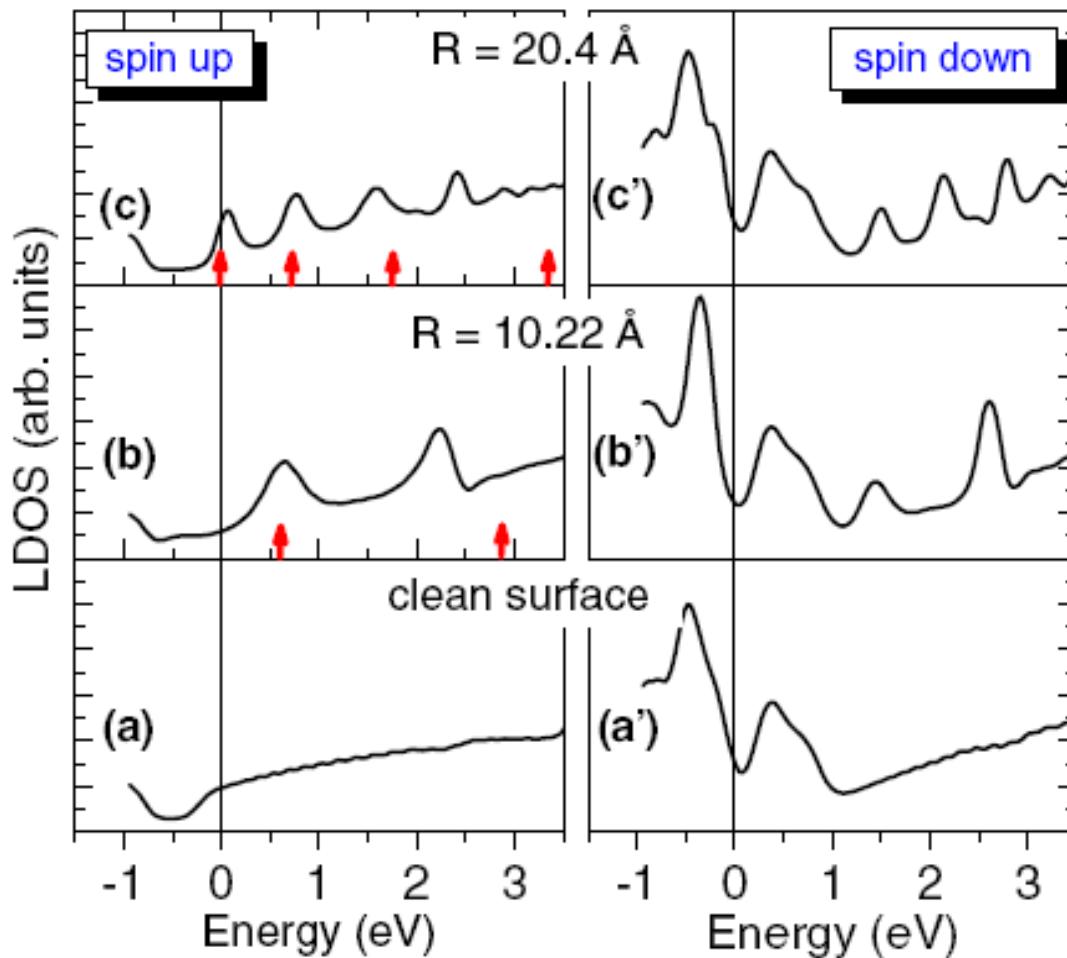
O. Pietzsch, A. Kubetzka, M. Bode, R. Wiesendanger, Science 292, 2053 (2001)



**Fig. 1.** Twelve images selected from a series of 24 taken at field values as indicated (17). Scan range is 200 nm by 200 nm. Because of the growth conditions (see text), a system of alternating ML and DL Fe stripes emerges on the W terraces. When measured with a ferromagnetic probe tip with perpendicular anisotropy, DL stripes show a two-stage contrast in the conductance map. It arises from the out-of-plane magnetization of DL stripes, being either parallel or antiparallel to the tip magnetization (spin valve effect). As a guide to the eyes, a dislocation line (a) is marked. Dark domains progressively vanish as positive field increases, and at saturation, only bright domains remain. High remanence is observed. A small negative field of -50 mT is sufficient to switch the tip magnetization whereas the sample stays almost unaffected. A contrast reversal results [compare (v) and (vi)]. At negative saturation, all stripes are once again bright (viii). Circles (b) and (c) refer to the enlarged views given in Figs. 3 and 4. Tunneling parameters:  $I = 0.5$  nA,  $U = +700$  mV.



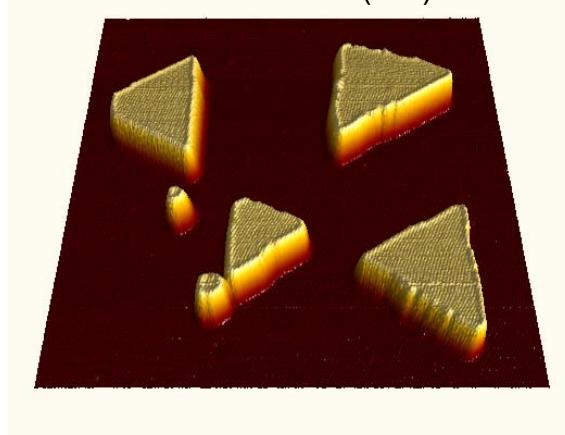
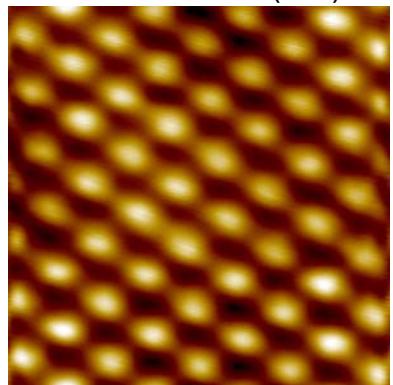
**Fig. 2.** Hysteresis curves obtained from the distribution of bright domains (A) and stripes with  $+z$  magnetization ( $\uparrow$ ) (B). The butterfly curve in (A) shows properties of the complete tunneling junction consisting of two ferromagnetic electrodes, whereas the curve in (B) displays only sample properties. Arrow symbols in (A) indicate the relative alignment of tip and sample magnetization. Roman numbers at solid circles correspond to the images shown in Fig. 1.



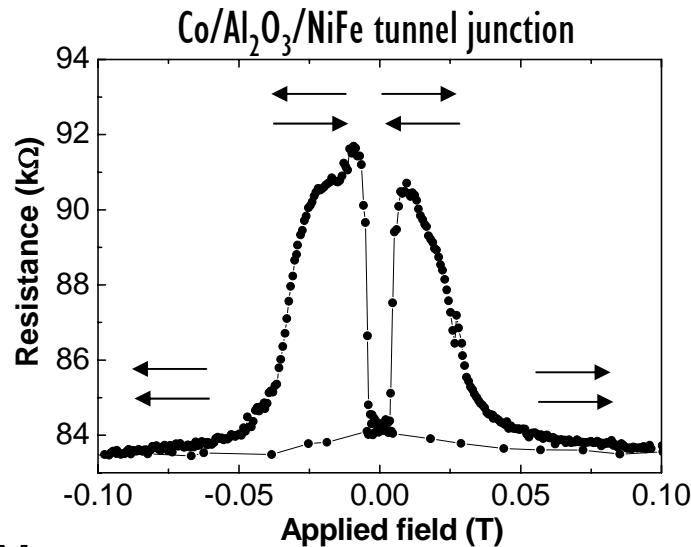
# Introduction: context of SP-STM

## Surface Science Scanning tunneling microscope

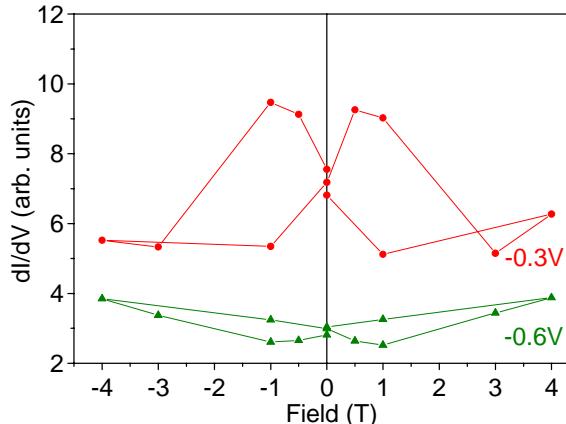
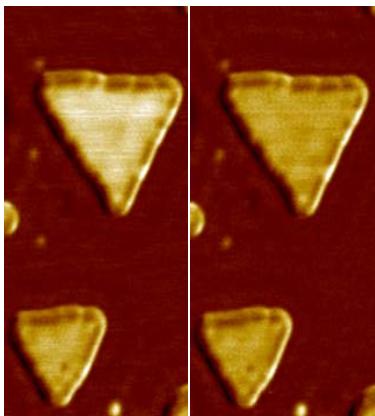
Atomic resolution Cu(111), 2x2nm   Co nanostructure on Cu(111) 50x50nm

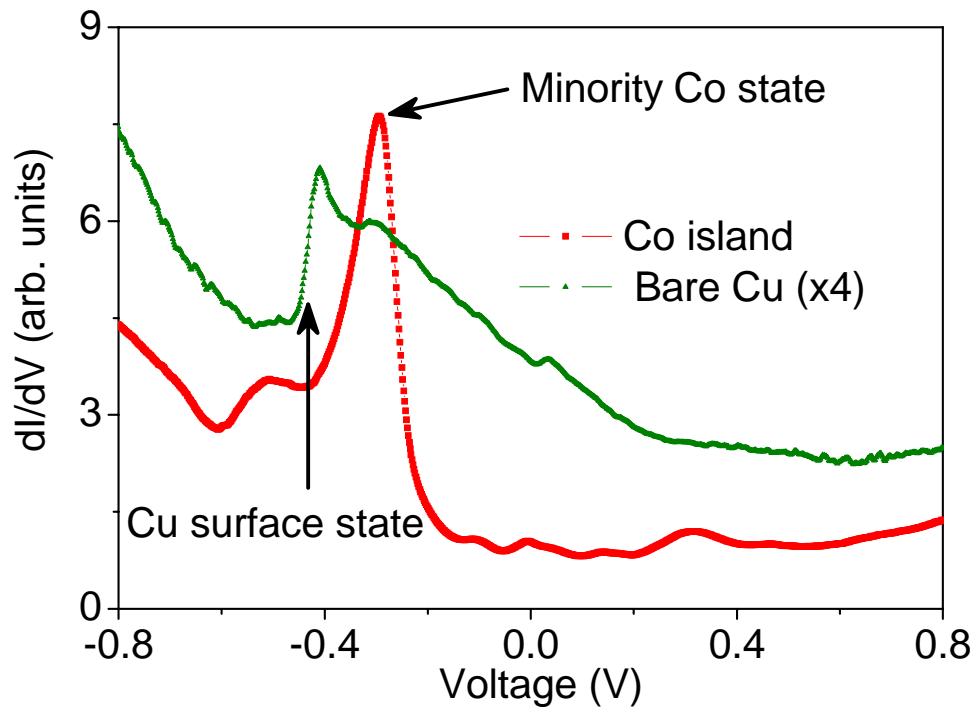


## Spintronic Tunnel Magnetoresistance



## Spin-polarized STM

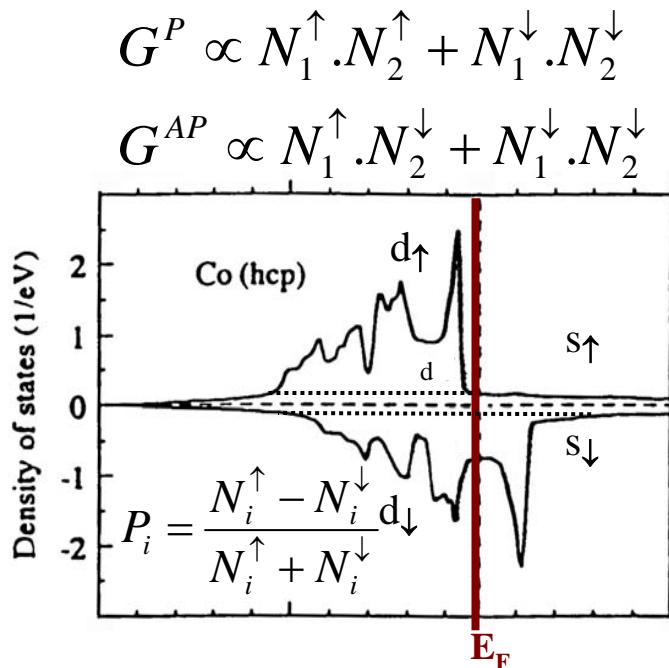




# Principle of TMR

Jullière model:

- Spin is conserved during tunneling
- Conductance  $\propto$  DOS of electrodes

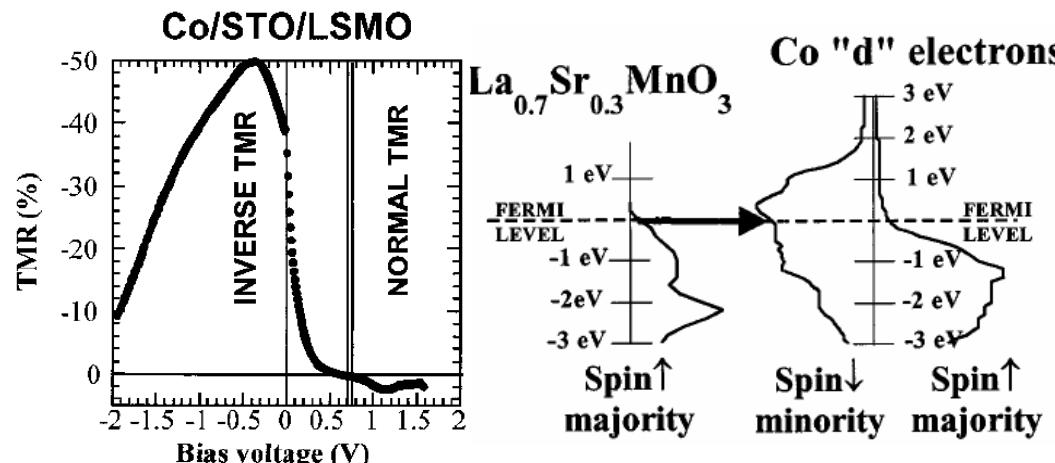


$$TMR \equiv \frac{G^P - G^{AP}}{G^P + G^{AP}} = P_1 P_2$$

$$G = G_0 (1 + P_1 P_2 \cos(\overrightarrow{M}_1, \overrightarrow{M}_2))$$

Open questions:

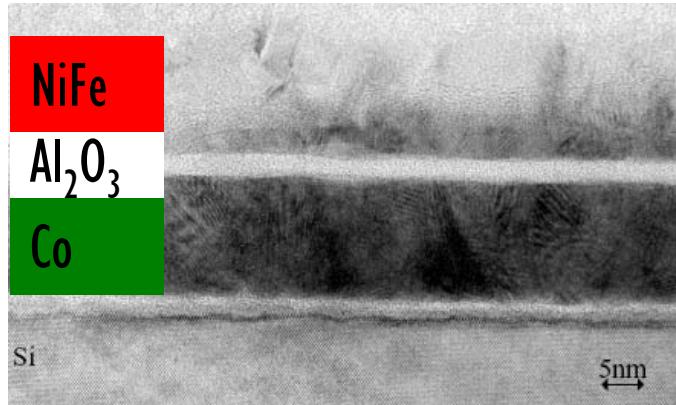
- TMR sign, depend only of  $P_1 P_2$  ?
- Interface electrode/barrier ?
- Voltage dependence ?
- Influence of the DOS ?



# Tunnel Magnetoresistance (TMR)

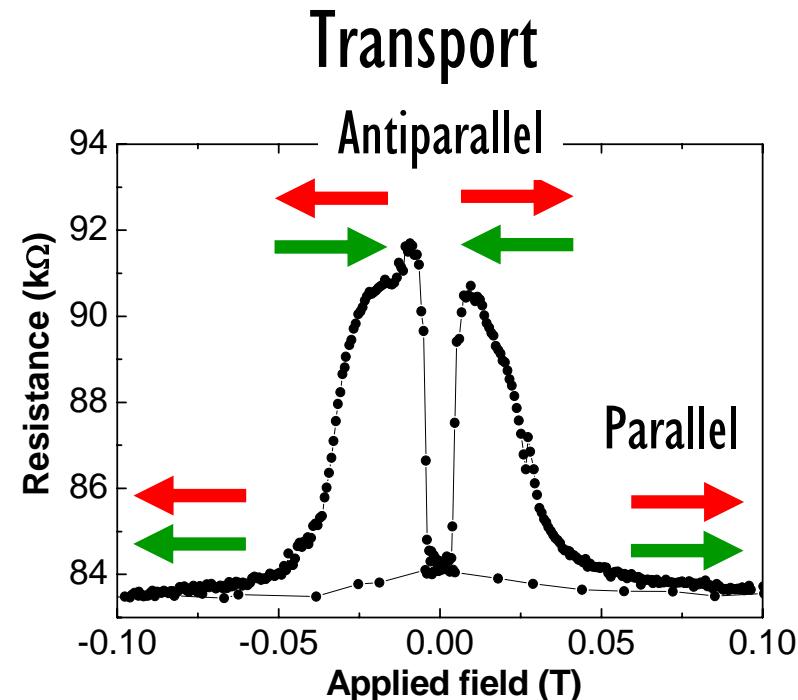
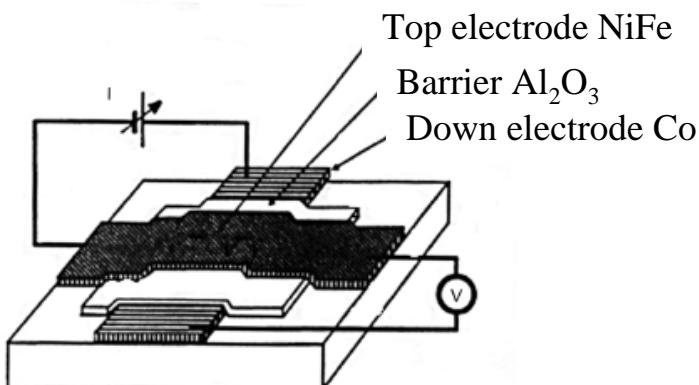
Jullière Phys. Lett. 54A, 225 (1975), Moodera et al. PRL 74, 3273 (1995)

## Trilayer: ferro/insulator/ferro

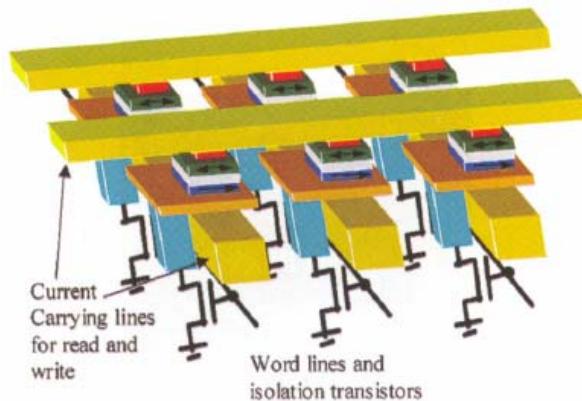


TEM view of a magnetic tunnel junction grown by sputtering

## Contacts made by lithography



## Application: MRAM

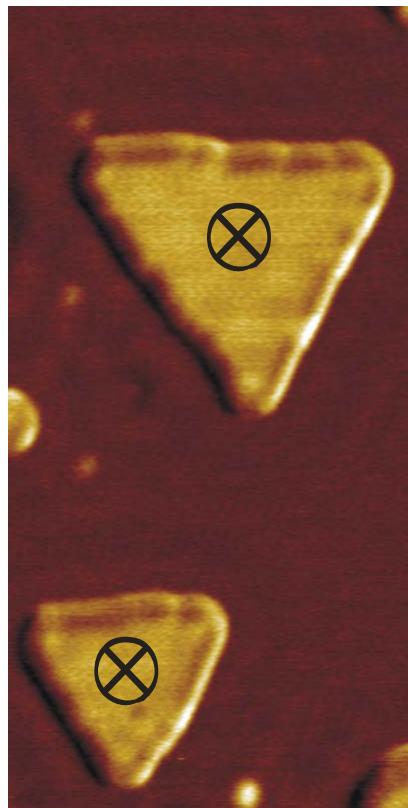


# Magnetic contrast

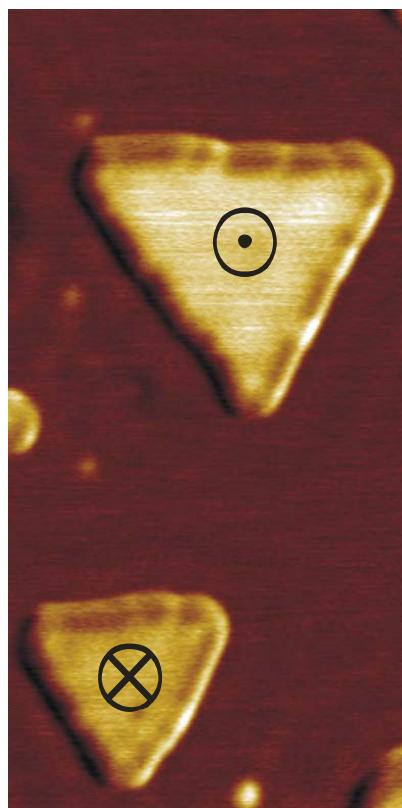
## External field out of plane

# Sample

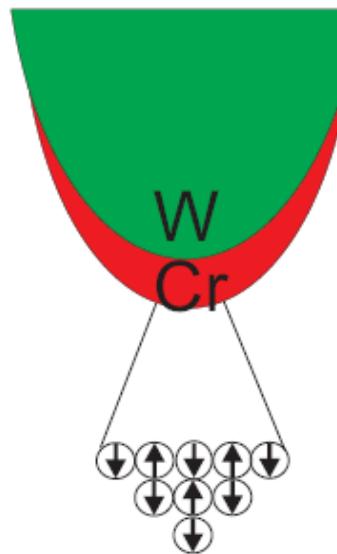
## « Parallel »



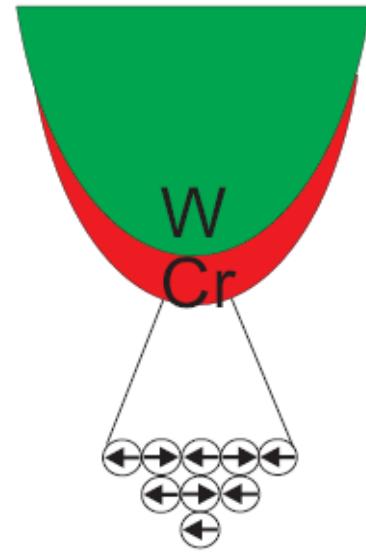
# « Antiparallel »



# Cr coated W tip



?

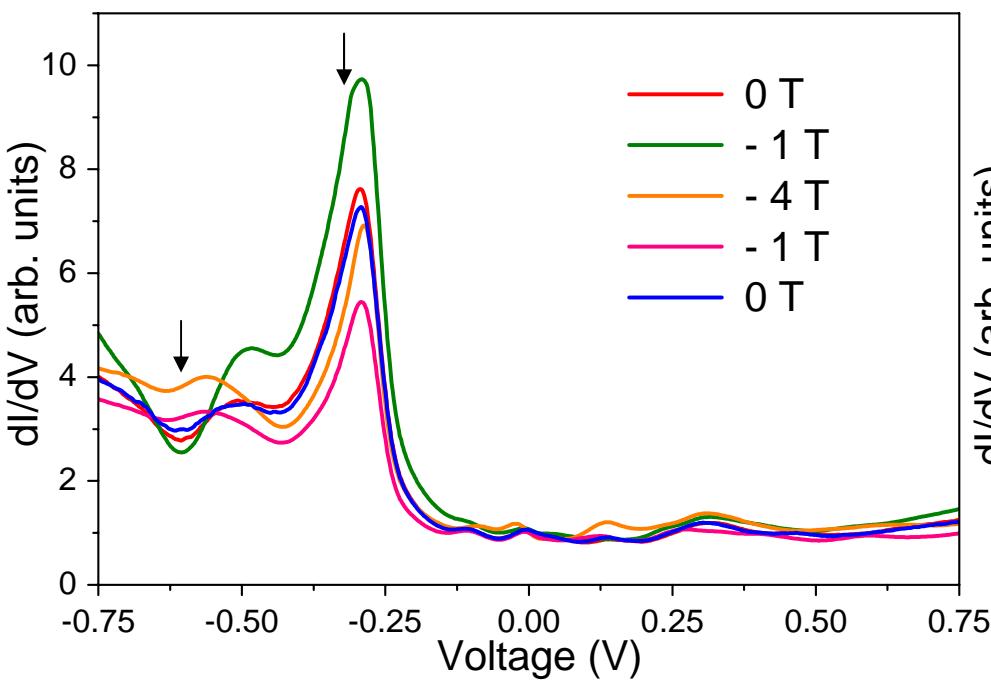


## SP-STM image: incomplete information on the magnetic configuration

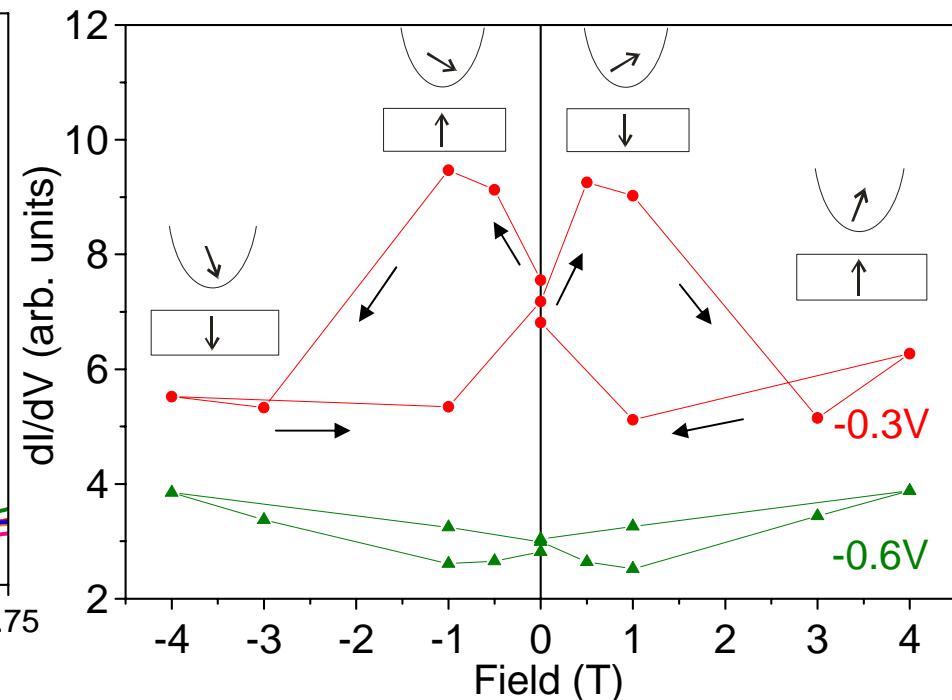
# Spin dependent transport on a single island

## $I(V)$ curves measured at island center

In field spectroscopy



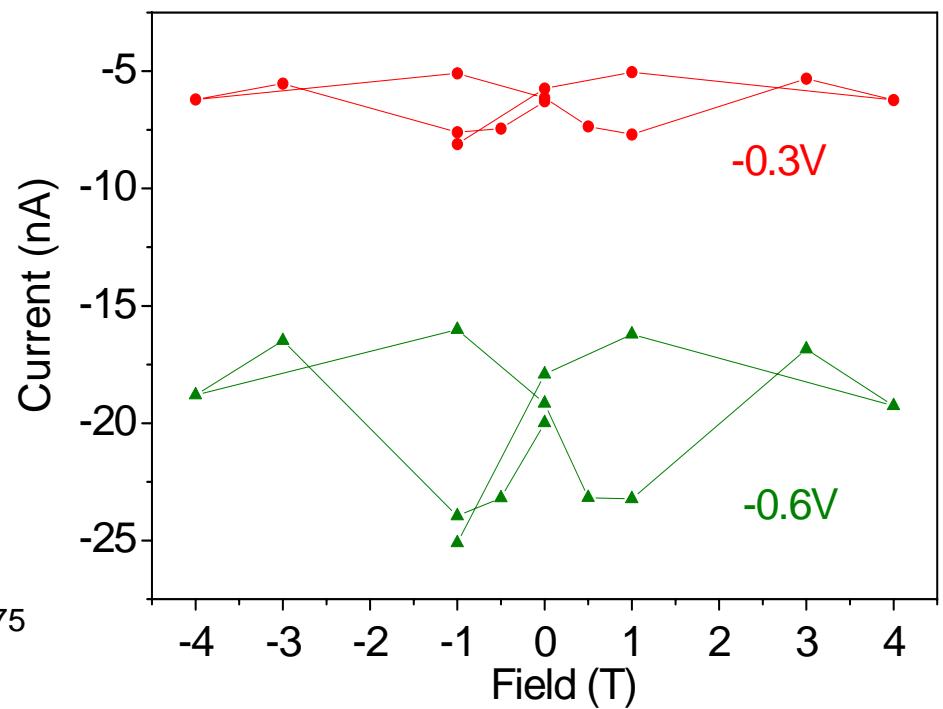
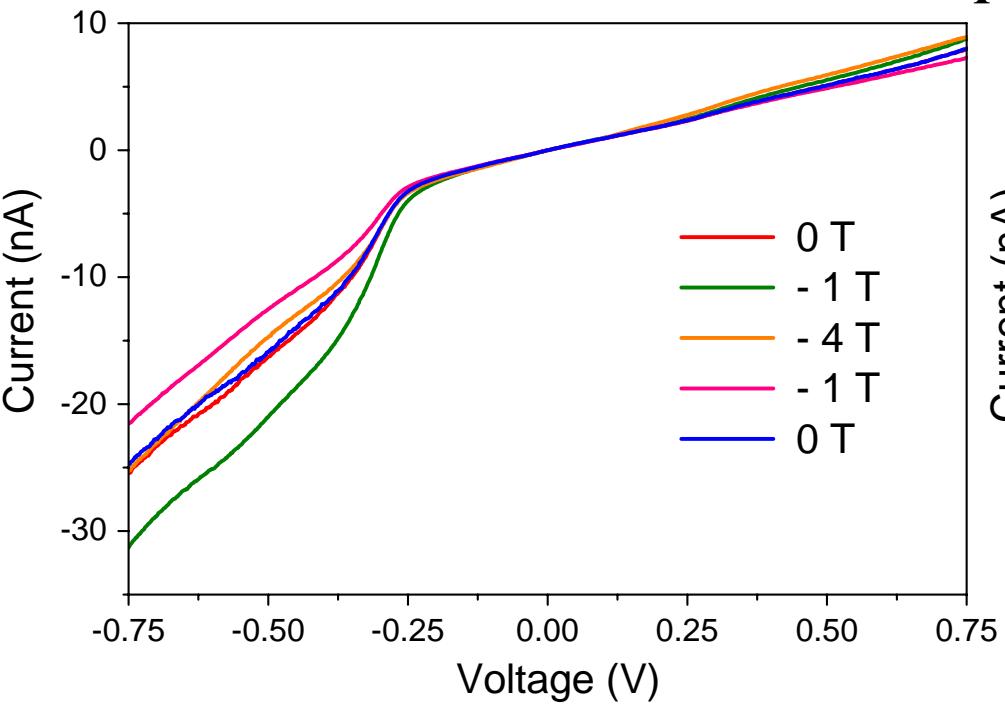
Extraction of the hysteresis cycle  
at different voltages



- Measure the relative magnetic orientation of tip and sample
- Understanding of the magnetic configurations, what is « parallel » and « antiparallel »

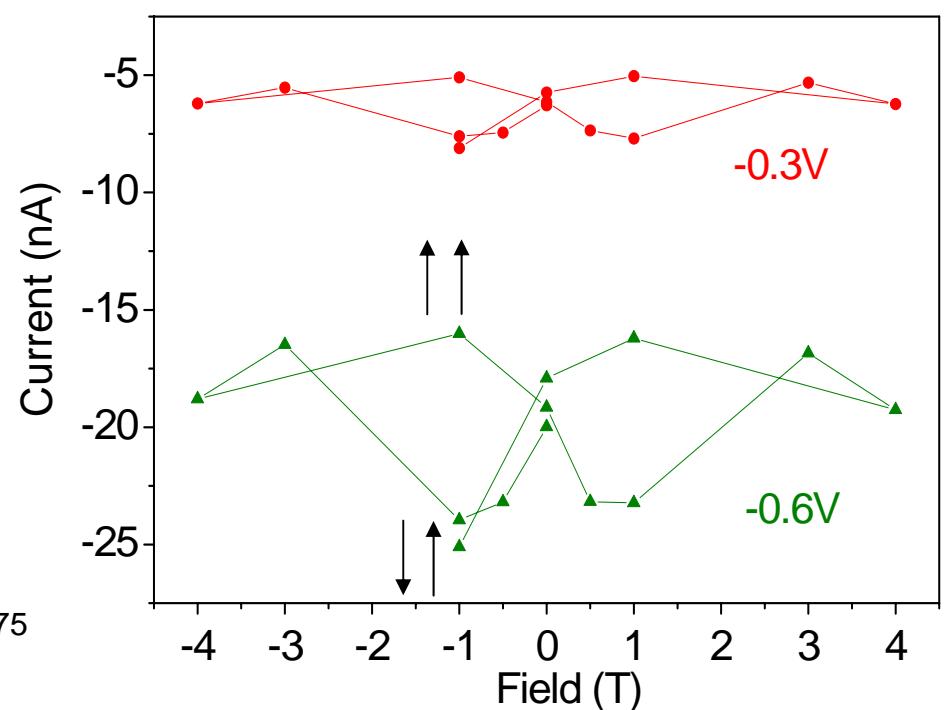
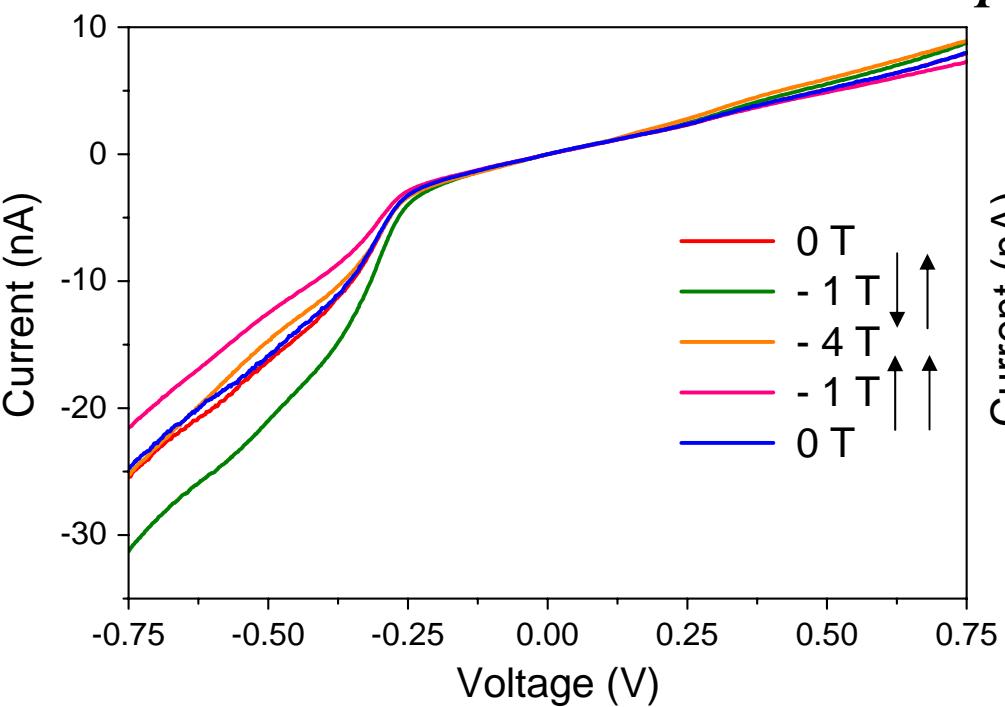
# TMR at a nanoscale

$$TMR \equiv \frac{I^P - I^{AP}}{I^P + I^{AP}}$$



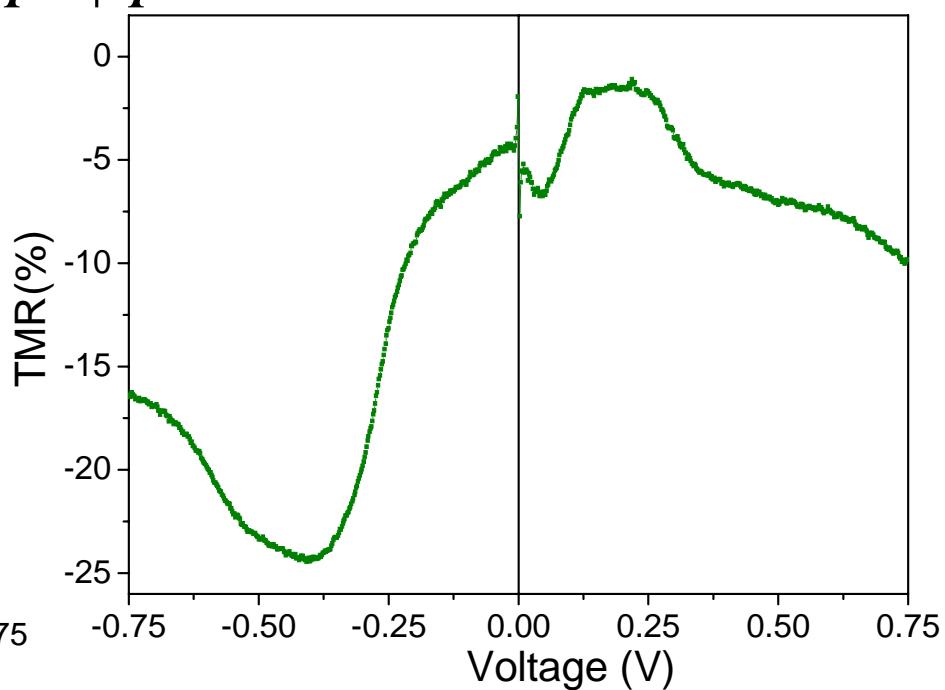
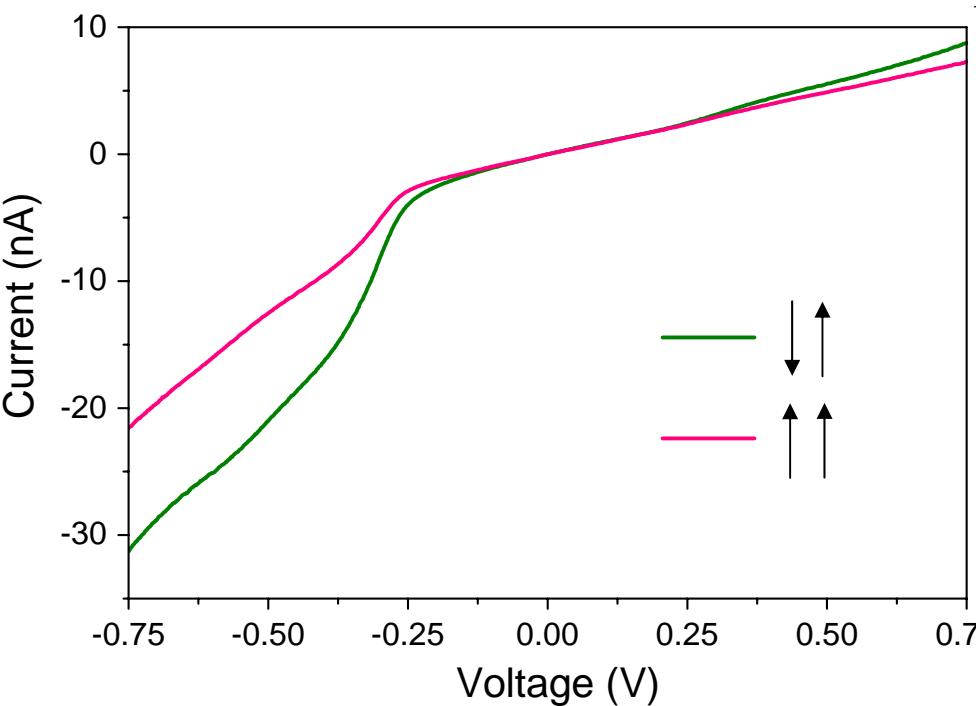
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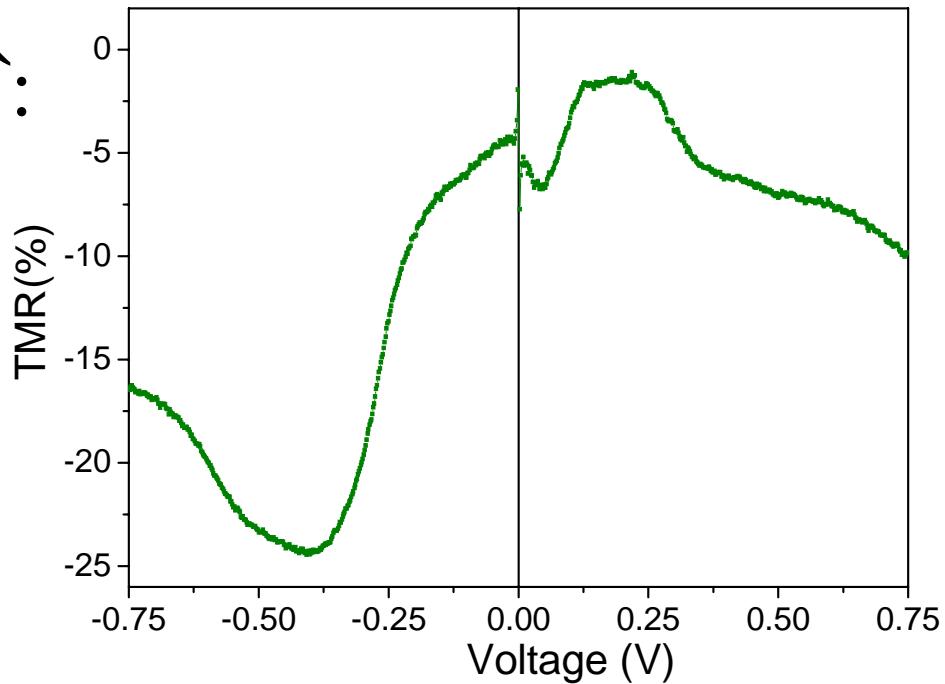
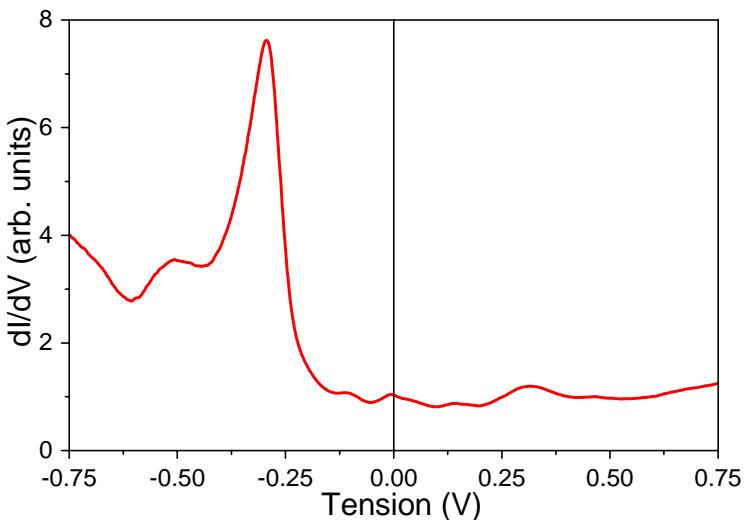
# TMR voltage dependence

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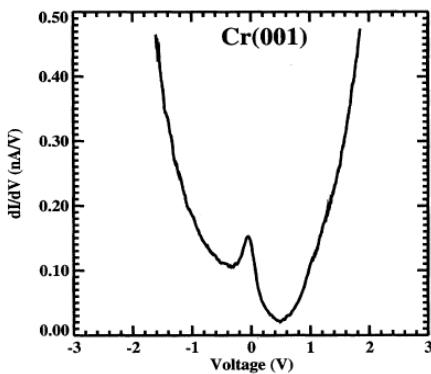
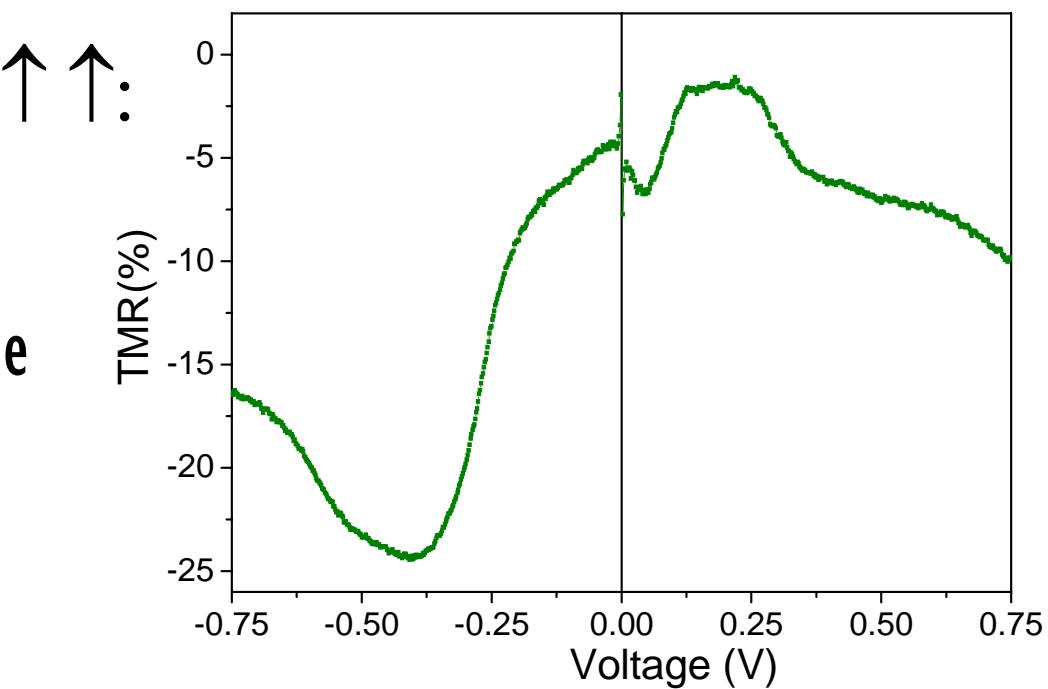
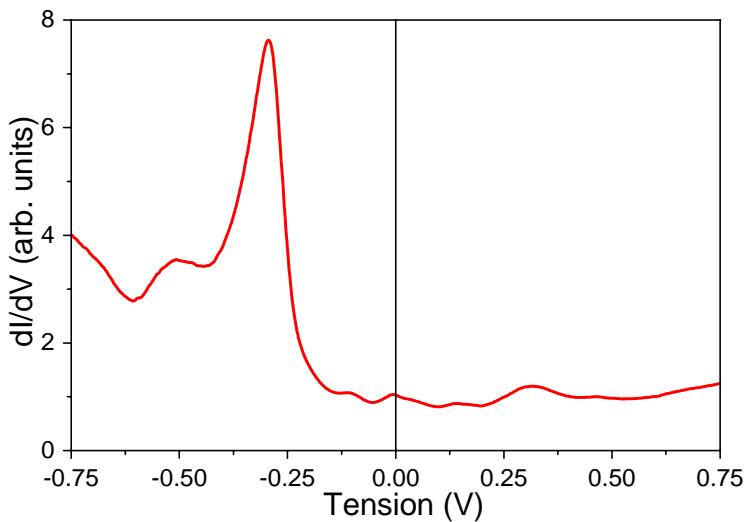
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- Higher current for  $\uparrow\downarrow$  than for  $\uparrow\uparrow\uparrow$ :  
TMR negative for all energy
- Shape can be understand from the LDOS dependence



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Stroscio et al. PRL 75, 2960 (1995)